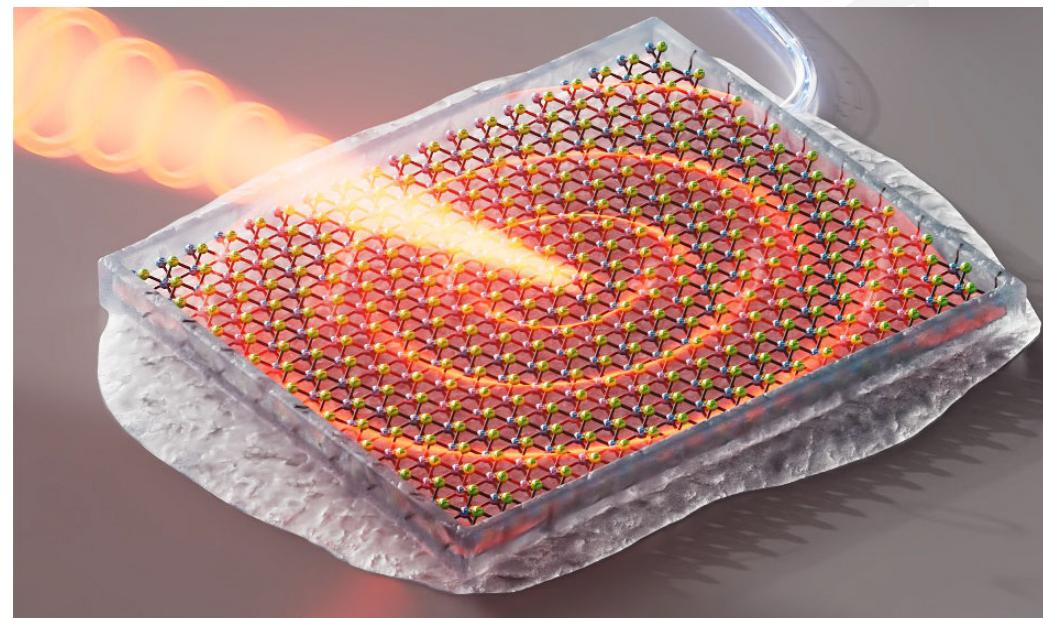


Optical Properties and Electron-Phonon Interactions in Low-Dimensional Materials

Vasili Perebeinos

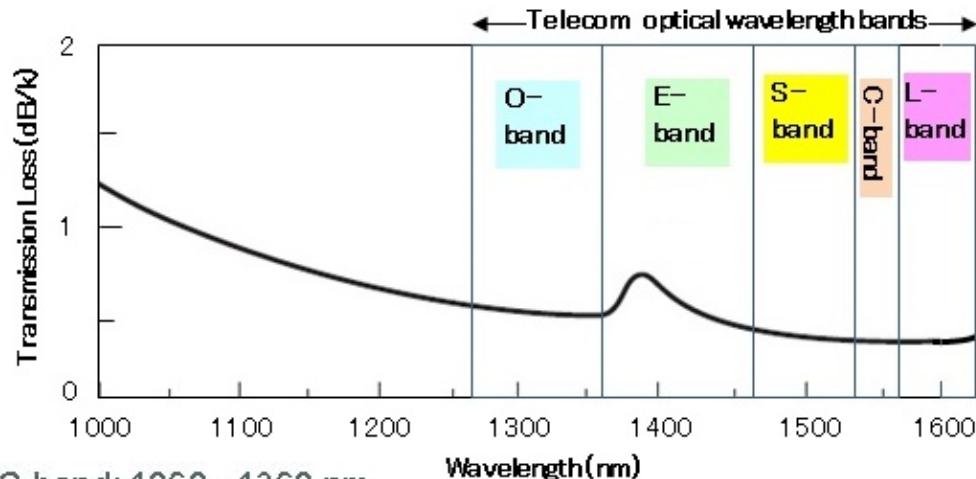
Electrical Engineering department

University at Buffalo, NY, USA



quest for 2D materials as quantum light generation

optical fiber attenuation



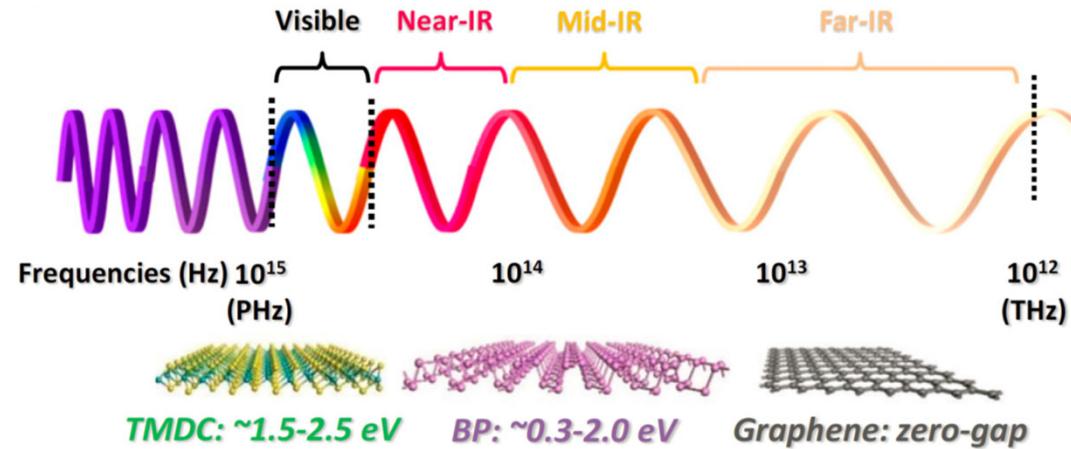
O-band: 1260 - 1360 nm

S-band: 1460 - 1530 nm

C-band: 1530 - 1565 nm

L-band: 1565 - 1625 nm

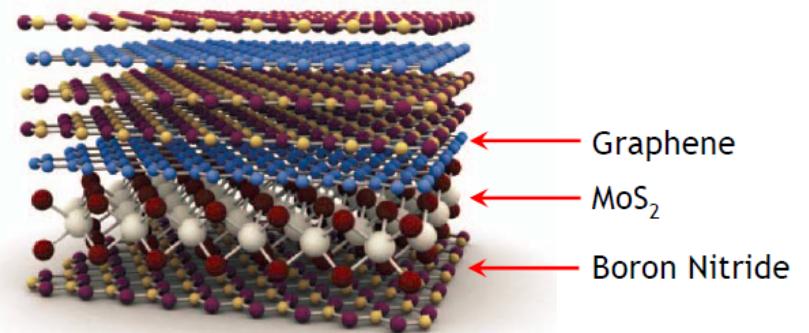
2D materials spectral range



Key Optical Properties of 2D Materials

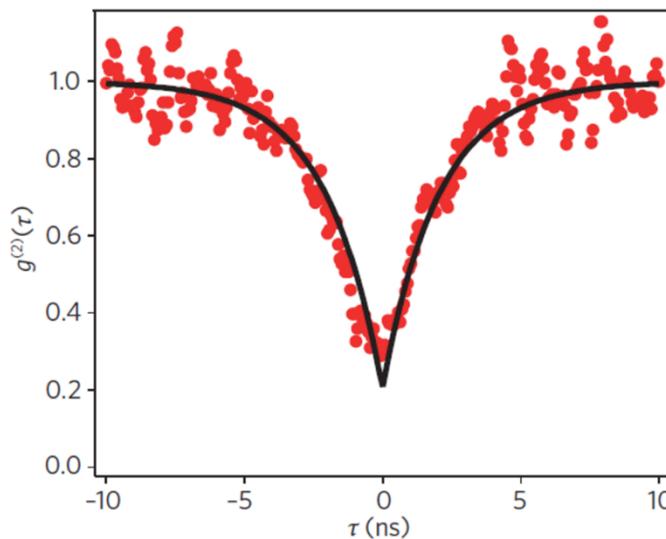
- Extraordinary strong light-mater interaction
- Strong electron-hole interactions, exciton binding up to 500 meV
- Strong optical nonlinearity
- Optical tuning external electric field
- Dielectric environment engineering

A schematic of a 2D hetero-structure



Novoselov et al, "A roadmap for graphene", Nature 2012

single photon emitters in WSe₂



Srivastava, et. al. *Nature Nano* **10**, 491 (2015)

He, et. al. *Nature Nano* **10**, 497 (2015)

Koperski, et. al. *Nature Nano* **10**, 503 (2015)

Chakraborty, et. al. *Nature Nano* **10**, 507 (2015)

Tonndorf, et. al. *Optica* **2**, 347 (2015)

METAL DICHALCOGENIDES

Two dimensions and one photon

Single-photon sources have been demonstrated in two-dimensional semiconductors.

V. Perebeinos

news & views

Nature Nano (2015)

Outline

- 1) Linear spectroscopy due to excitons and trions
- 2) Phonon-Assisted Indirect Exciton Ionization in 2D materials
- 3) Electron-phonon interactions in mono and bilayer graphene
- 4) Electron-phonon interactions in black phosphorous and 1D SbPS4

excitons in 3D, 2D, and 1D

$$E_n^{3D} = -E_0 \frac{1}{n^2}, E_0 = 13.6 \text{ eV} \frac{m}{\epsilon^2}, a_B = 0.529 \text{ \AA} \epsilon/m$$

$$E_n^{2D} = -E_0 \frac{1}{(n + 1/2)^2}$$

$$E_\lambda^{1D} \propto -E_0 \ln\left(\frac{d}{a_B}\right)$$

GaAs: $E_1 = 4.2 \text{ meV (3D)}$

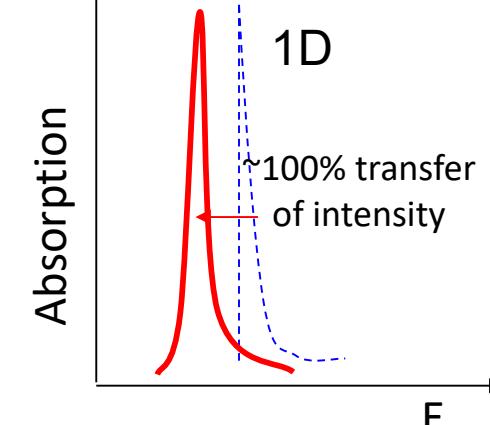
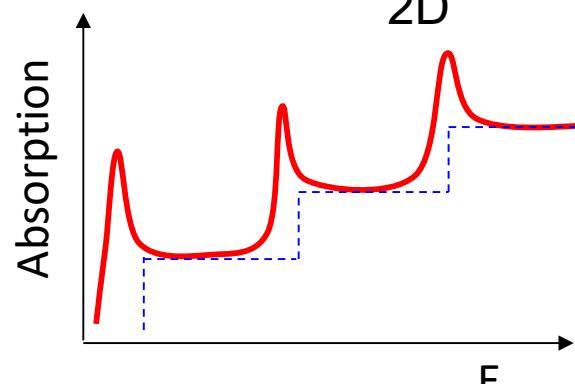
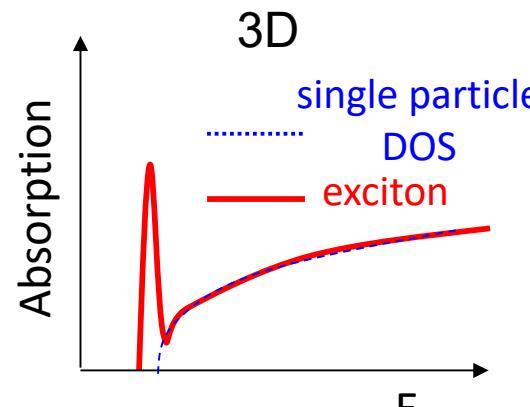
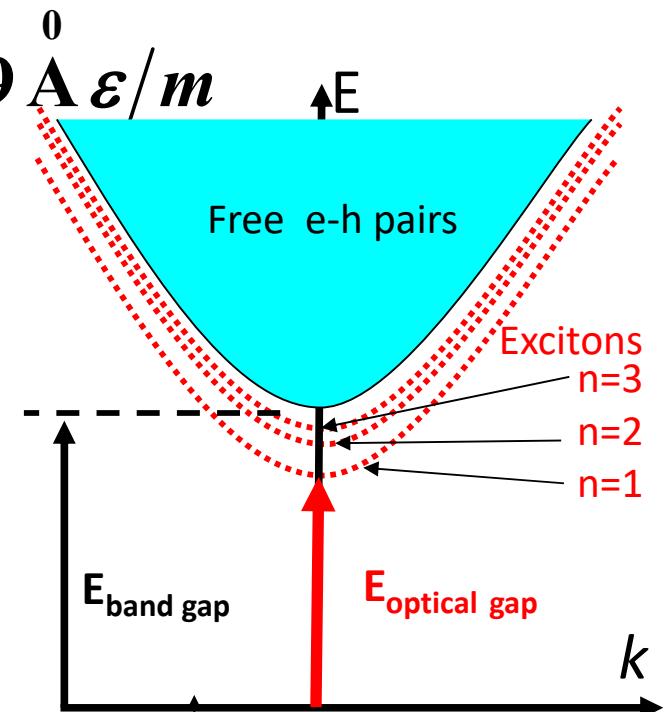
GaAs: $E_1 = 16.8 \text{ meV (2D)}$

CNT $E_1 \sim 500 \text{ meV (1D)}$

$$E_B \sim 1/(d\epsilon^{1.4})$$

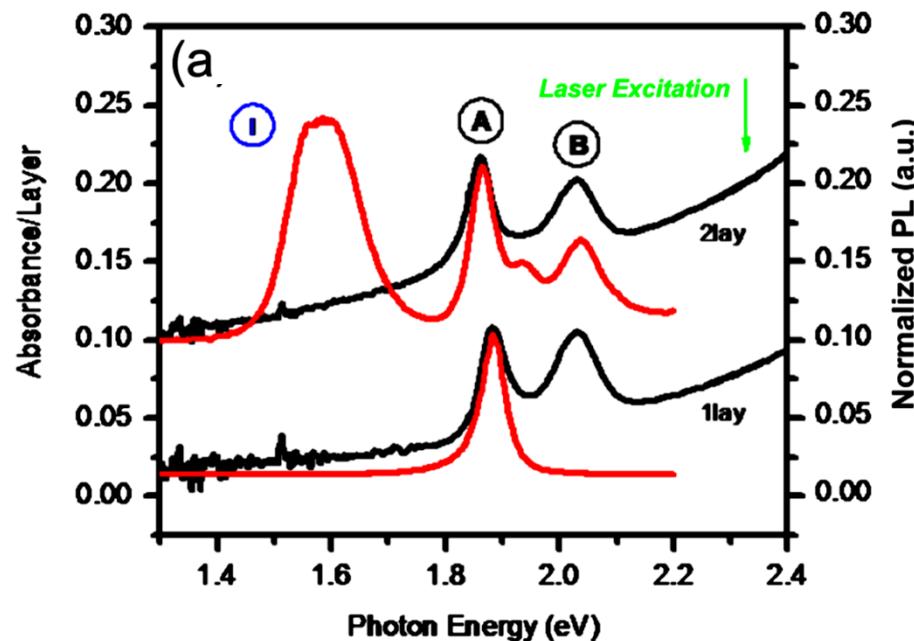
Perebeinos et. al. PRL (2004)

See also: Zhao and Mazumdar PRL (2004)

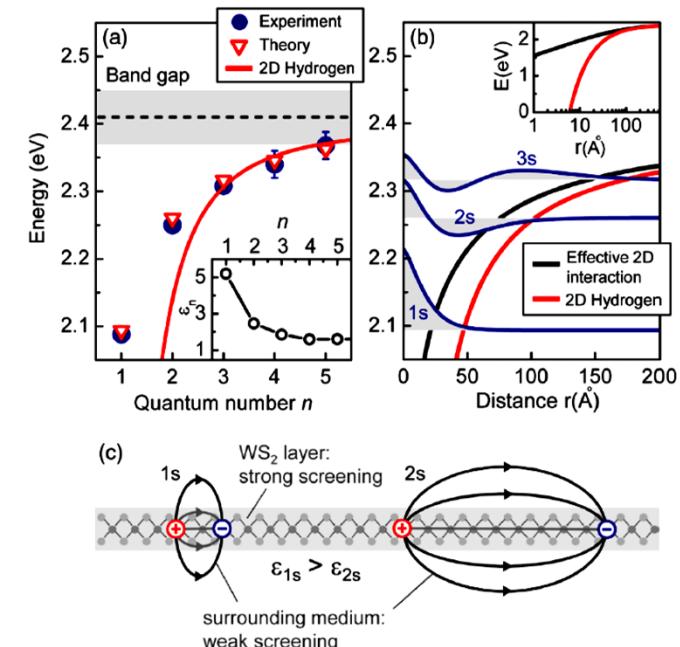


Avouris, Freitag, Perebeinos, *Nature Photonics* 2, 341 (2008)

excitons in transition metal dichalcogenides



K.F. Mak, et al., Phys. Rev. Lett. **105**, 136805 (2010)



A. Chernikov, et al., Phys. Rev. Lett. **113**, 076802 (2014)

Excitons and trions with large binding energies

Experiments:

- K. F. Mak, et al., Nat. Mater. **12**, 207 (2013)
- Z. Ye, et al., Nature **513**, 214 (2014)

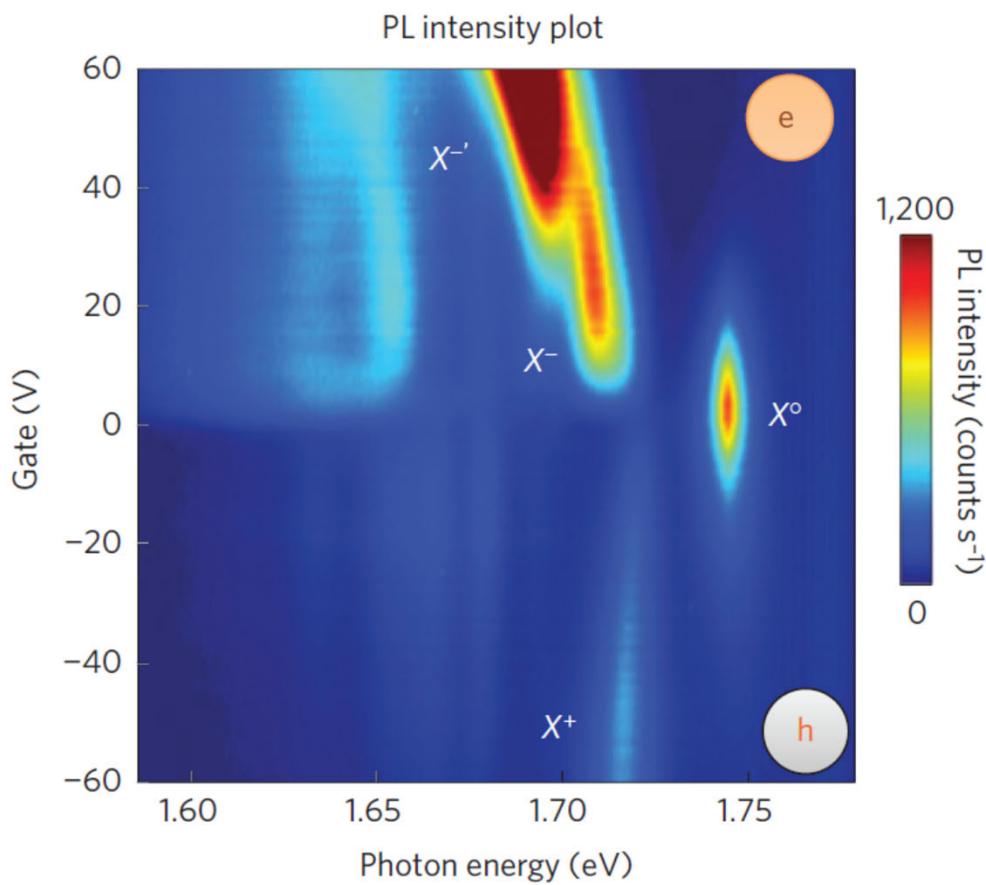
Theory:

- T. C. Berkelbach, et al., Phys. Rev. B **88**, 045318 (2013)
- D. Y. Qiu, et al., Phys. Rev. Lett. **111**, 216805 (2013)

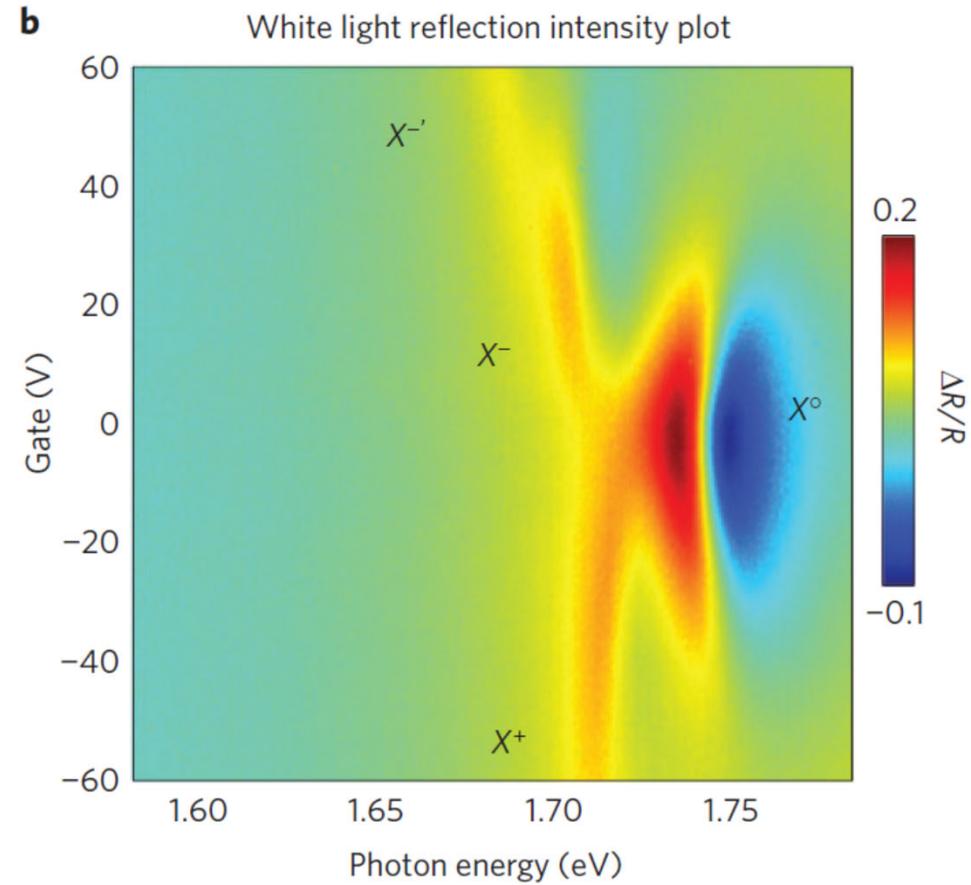
and many others...

trions in transition metal dichalcogenides

a



b



theoretical approach for excitons

$$|nk\rangle = \frac{1}{\sqrt{N}} \sum_{v,i} e^{ik \cdot R_i} a_{nkv} |v, R_i\rangle \quad \text{single-particle basis set}$$

$$\Delta_{vck} A_{vck}^S + \sum_{v'c'k'} \mathcal{K}_{vck, v'c'k'} A_{v'c'k'}^S = \Omega_S A_{vck}^S \quad \text{Bethe-Salpeter equation for two-particle wavefunction}$$

$$\mathcal{K}_{vck, v'c'k'} = \mathcal{K}_{vck, v'c'k'}^d + \mathcal{K}_{vck, v'c'k'}^x \quad \begin{array}{l} \text{interaction kernel:} \\ \text{direct and exchange Coulomb potentials} \end{array}$$

$$W(|R_{ij}^{vv'}|) = \frac{e^2}{8\varepsilon_0 r_0} \left[H_0\left(\frac{\varepsilon |R_{ij}^{vv'}|}{r_0}\right) - Y_0\left(\frac{\varepsilon |R_{ij}^{vv'}|}{r_0}\right) \right] \quad \text{the Struve and Bessel functions}$$

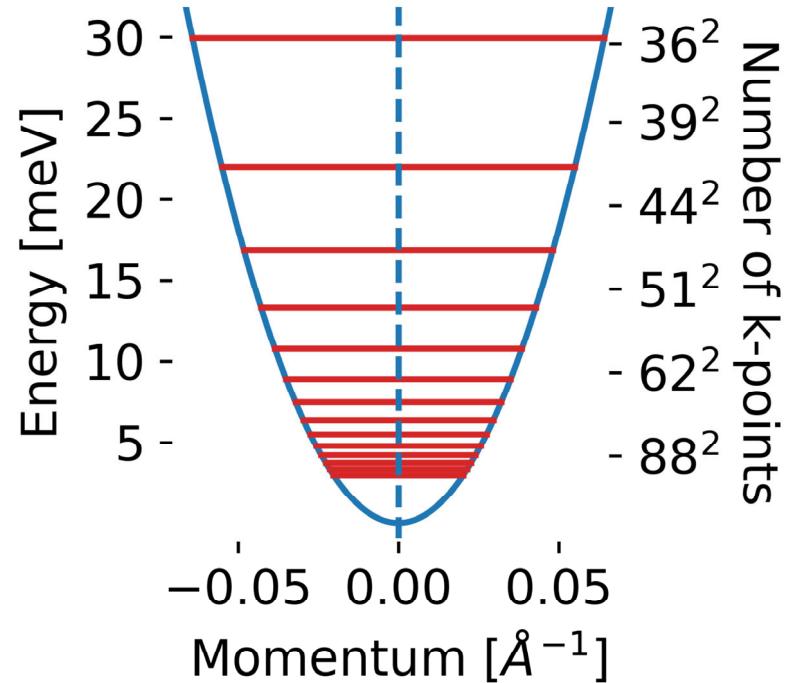
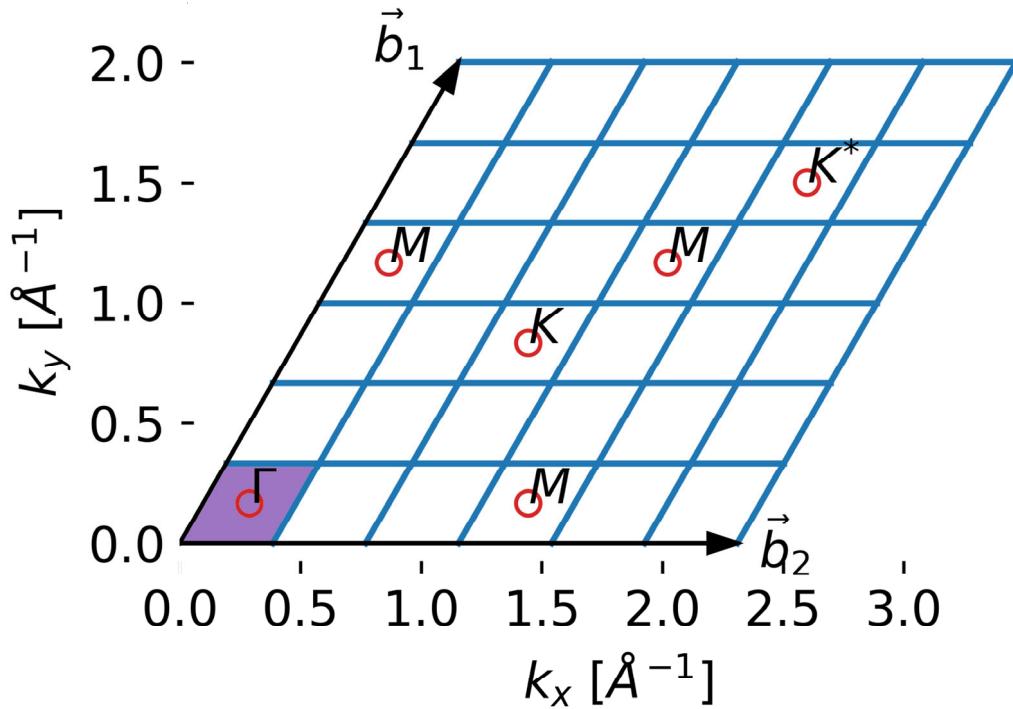
$$r_0 = 2\pi \chi_{2D} \quad \text{screening from 2D material: } \chi_{2D} = 6.5 \text{ \AA}$$

$$\varepsilon = (\varepsilon_1 + \varepsilon_2)/2 \quad \begin{array}{l} \text{screening from the background:} \\ \varepsilon_1 \text{ and } \varepsilon_2 \text{ are above and below the 2D material} \end{array}$$

$$|\Psi_S\rangle = \sum_{vck} A_{vck}^S \hat{c}_{ck}^\dagger \hat{c}_{vk} |\text{GS}\rangle \quad \text{exciton two-particle wavefunction}$$

$$\alpha(\omega) = \frac{e^2 \pi}{\varepsilon_0 c \omega} \frac{1}{A} \sum_S \left| \sum_{vck} A_{vck}^S d_{vc}(\mathbf{k}) \right|^2 \delta(\hbar\omega - \Omega_S) \quad \text{absorption spectra}$$

trions calculations

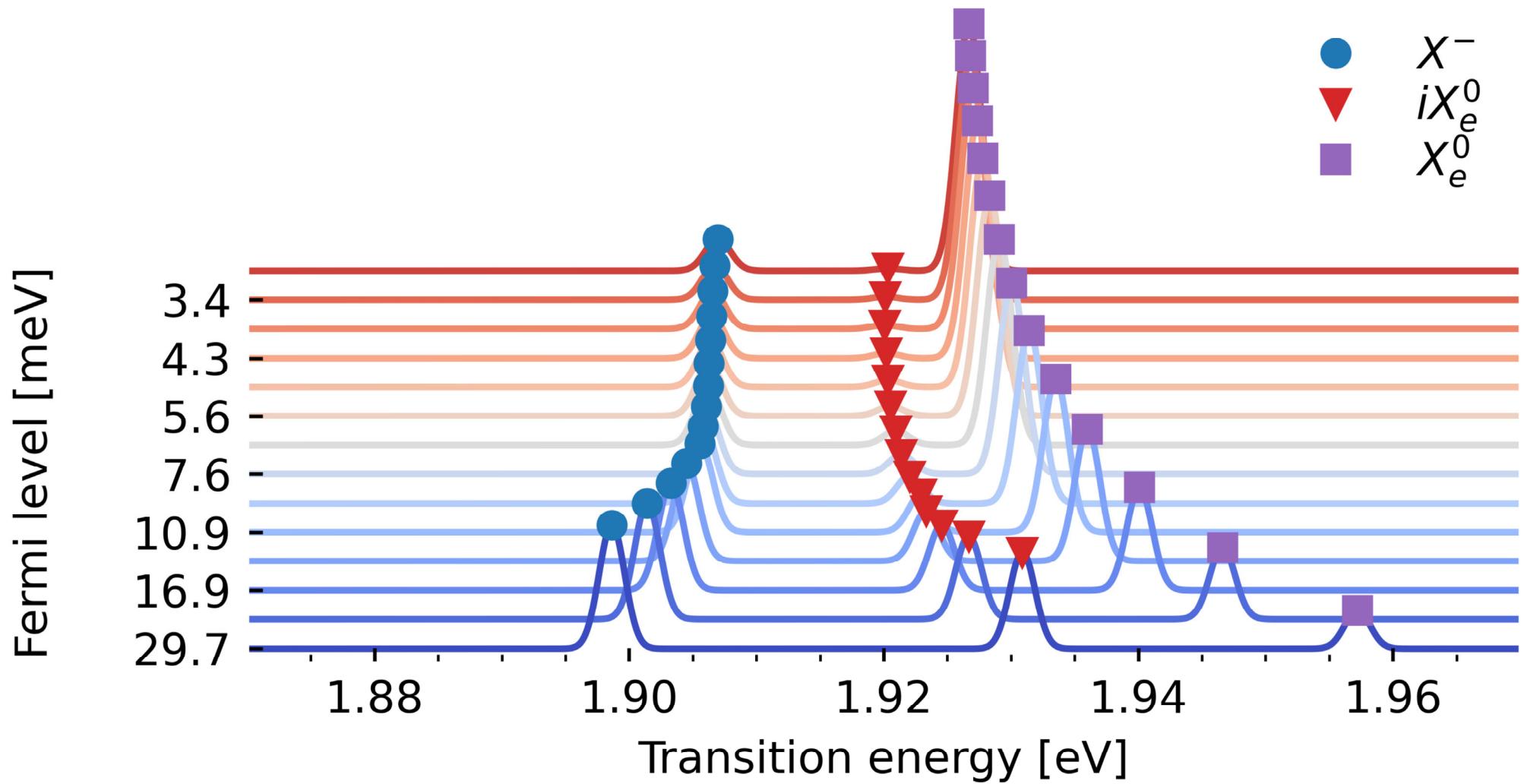


Trion Hamiltonian:

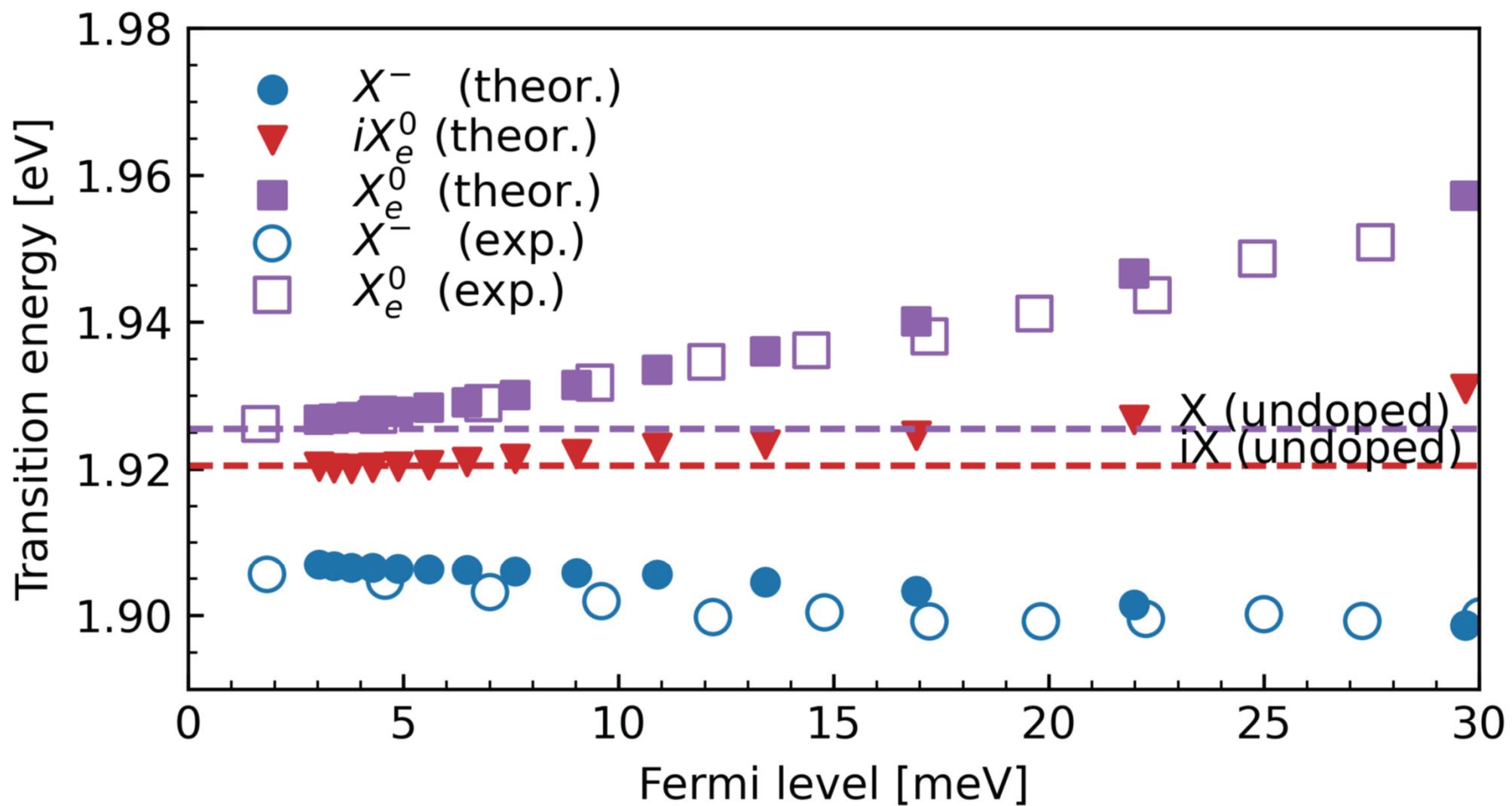
$$\langle v c_1 c_2 | H^{Trion} | v' c'_1 c'_2 \rangle = \langle v c_1 c_2 | H_{kin} | v c_1 c_2 \rangle + \langle v c_1 c_2 | H_{c1c2} | v' c'_1 c'_2 \rangle + \\ \langle v c_1 c_2 | H_{c1v} | v' c'_1 c_2 \rangle + \langle v c_1 c_2 | H_{c2v} | v' c_1 c'_2 \rangle$$

$$\langle T, \mathbf{K} | \mathbf{p} | c, \mathbf{K} \rangle = \sum_{vc_1 c_2} A_{vc_1 c_2}^{(T, \mathbf{K})} (\mathbf{p}_{vc_1} \delta_{c\mathbf{K}, c_2} - \mathbf{p}_{vc_2} \delta_{c\mathbf{K}, c_1})$$

doping dependence of linear absorption spectra in MoS₂



Doping dependence of trions and excitons

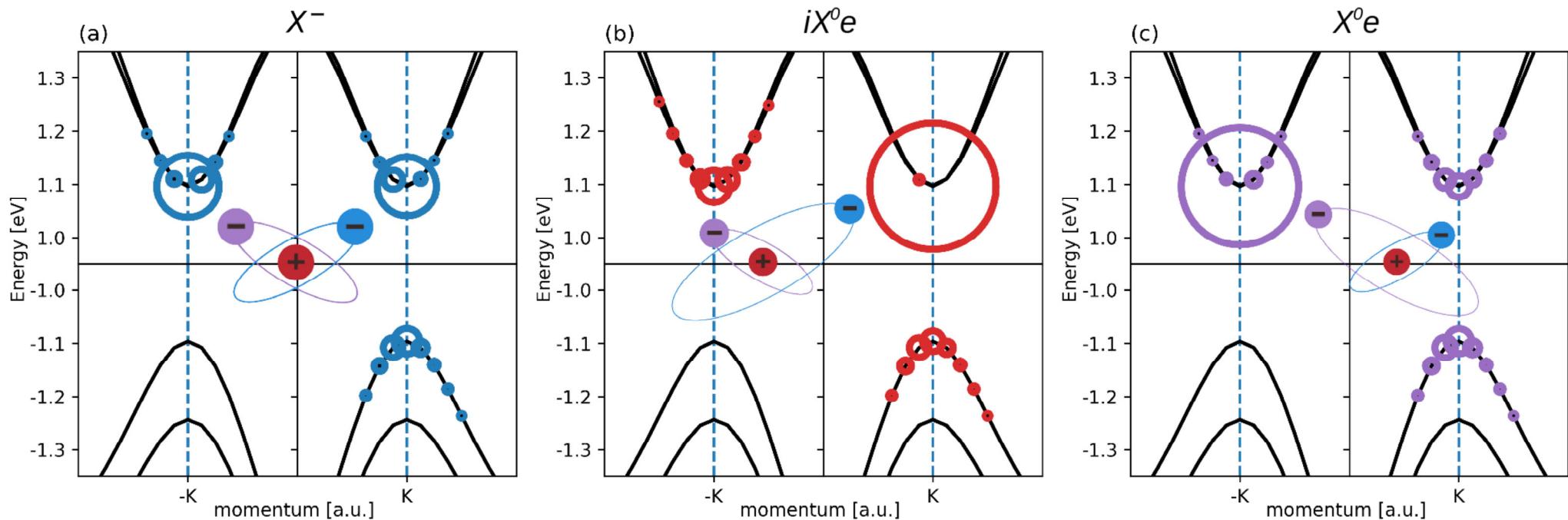


Exp: K.F. Mak, et. al. *Nat. Materials* **12**, 207 (2012)

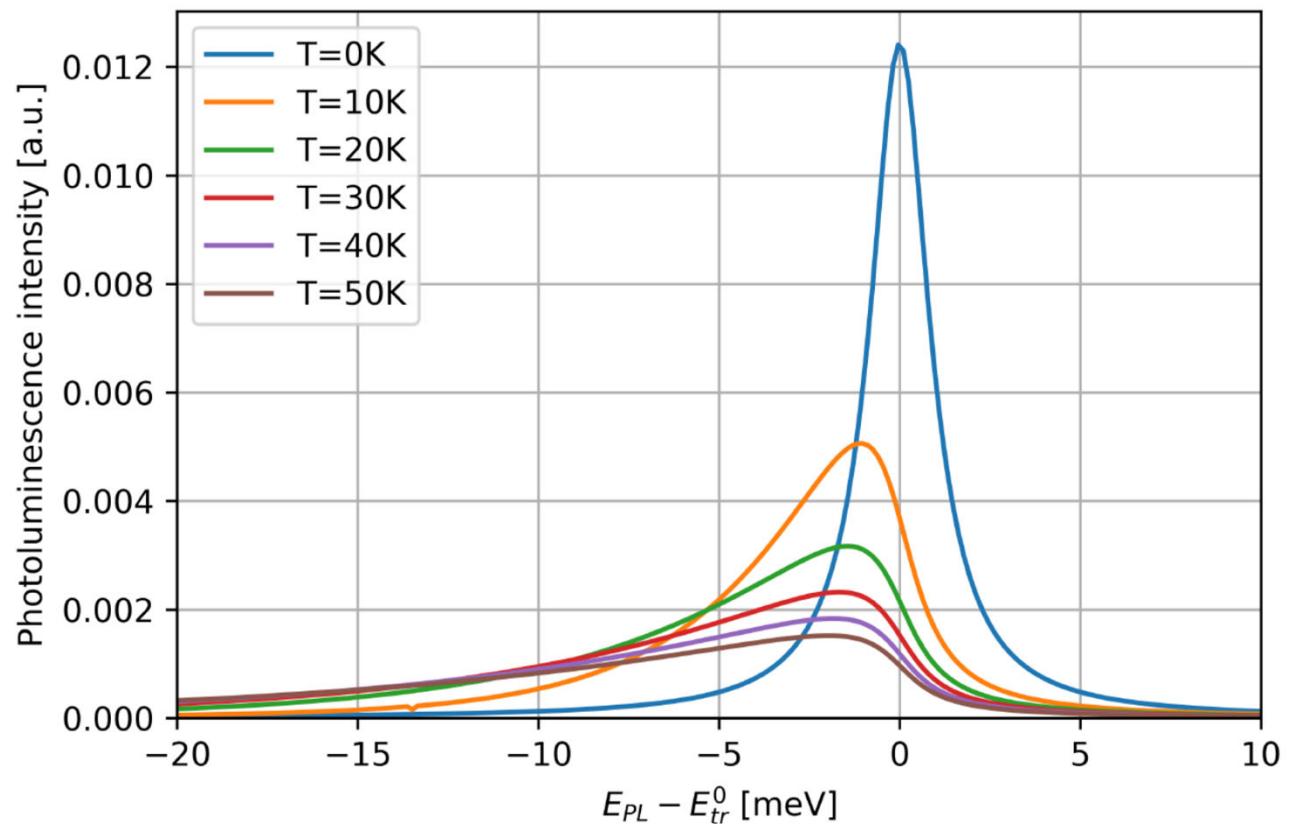
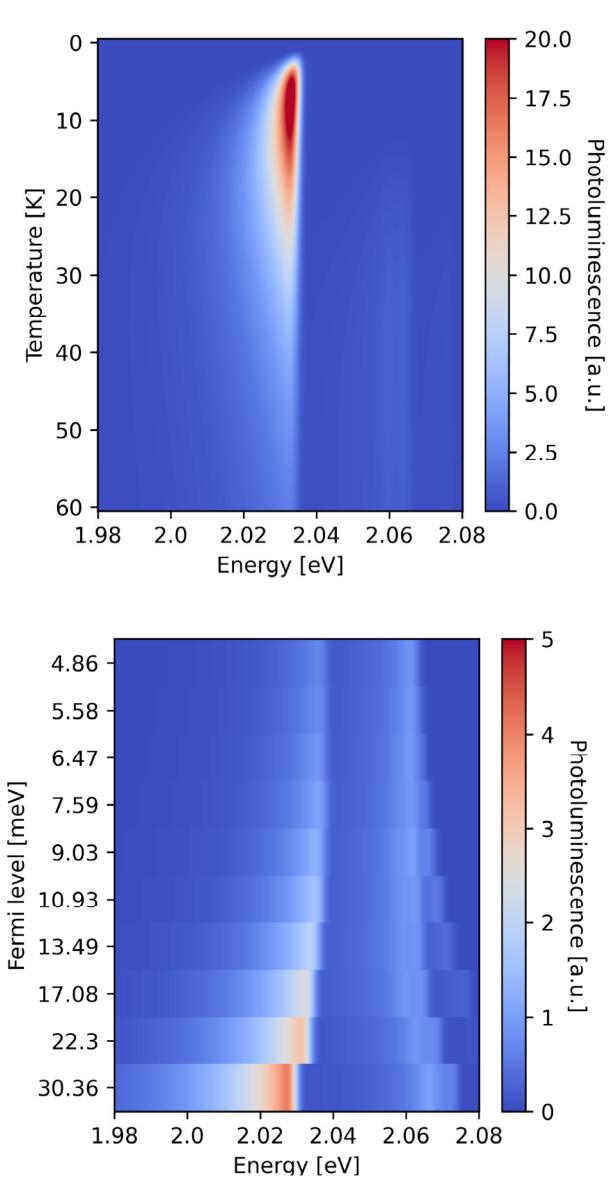
Theory: Zhumagulov, et. al. *Phys. Rev. B* **101**, 245433 (2020)

Three-particle wavefunctions

Structure of trion states: single-particle density of states
circle positions - contributing state, circle radius - weight



Temperature dependence of PL spectrum

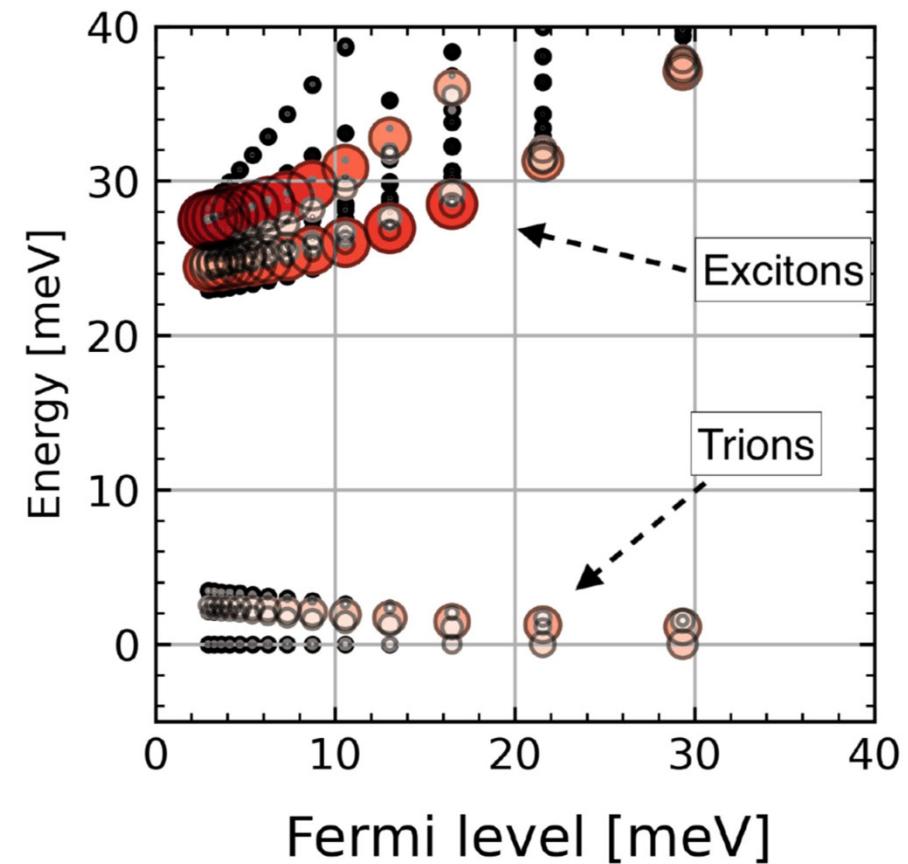
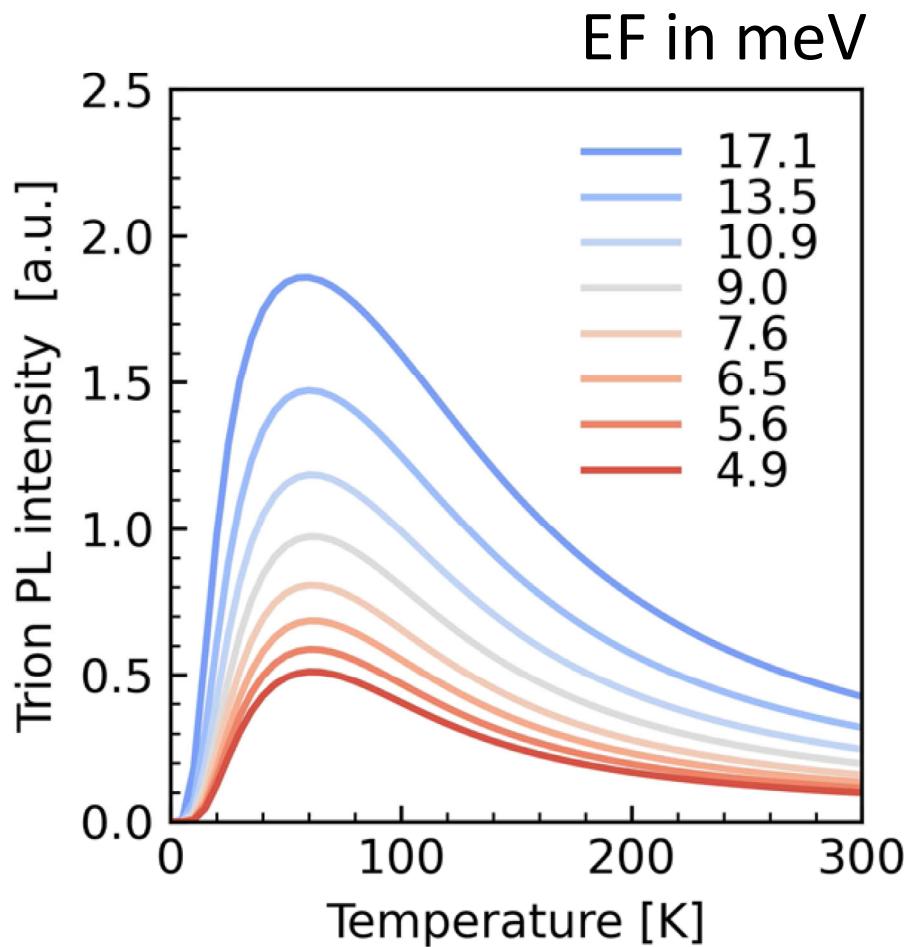


$$\Omega(|T, \mathbf{K}\rangle \rightarrow |c, \mathbf{K}\rangle) = E^{(T, \mathbf{K})} - \varepsilon_{(c, \mathbf{K})}$$

$$L(E) \sim \sum_{(c\mathbf{K}, T\mathbf{K})} |\langle T, \mathbf{K} | \mathbf{p} | c, \mathbf{K} \rangle|^2 \times \delta(E - \Omega(|T, \mathbf{K}\rangle \rightarrow |c, \mathbf{K}\rangle)) \quad w(q)$$

$$w(q) = \frac{1}{Z} e^{-\frac{E_T(q)}{kT}} \quad Z = \int_{BZ} e^{-\frac{E_T(q)}{kT}}$$

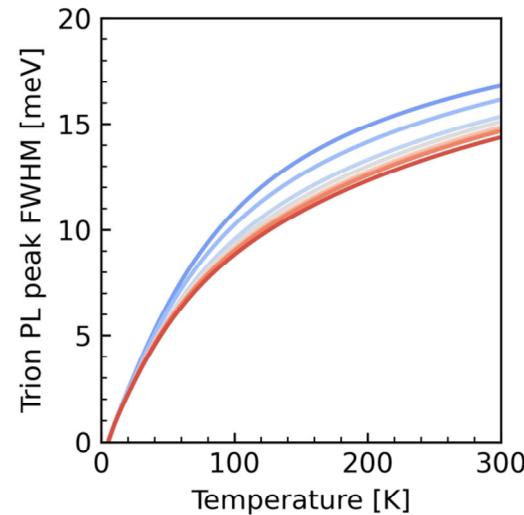
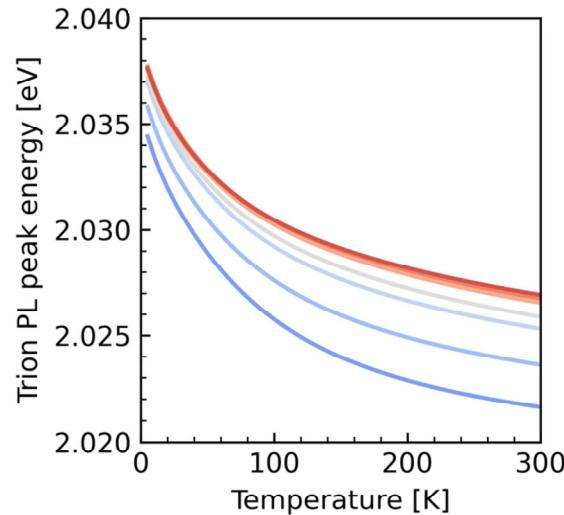
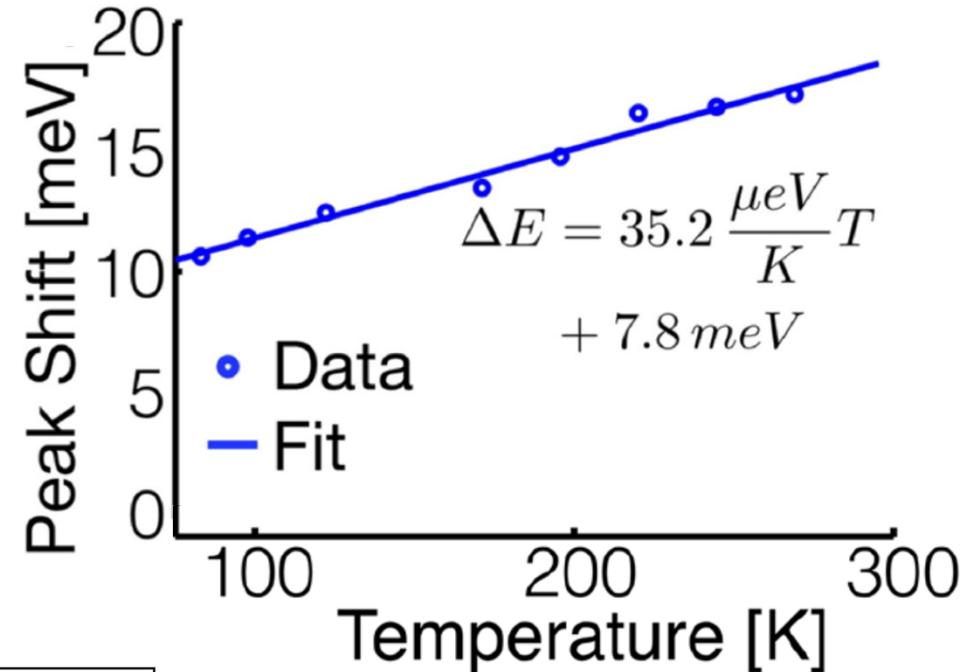
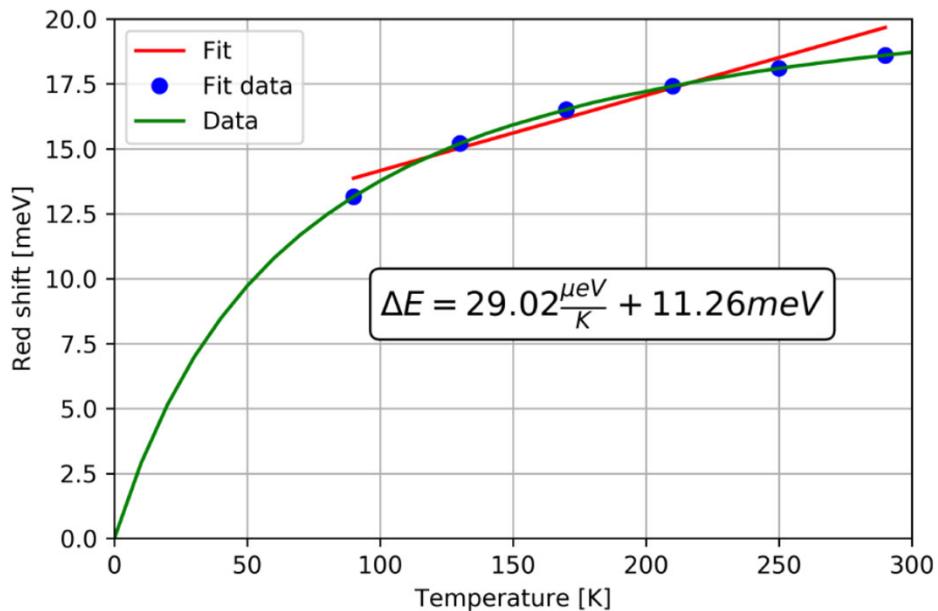
Temperature dependence of PL spectrum



Zhumagulov, et. al. *J. Chem. Phys.* **153**, 044132 (2020)

Zhumagulov, et. al. *Nanomaterials* **12**, 3728 (2022)

comparison with the experiment



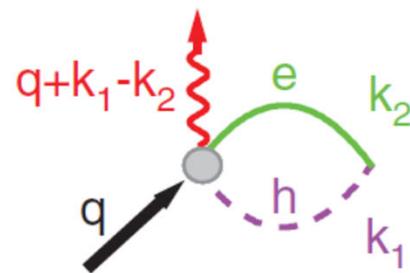
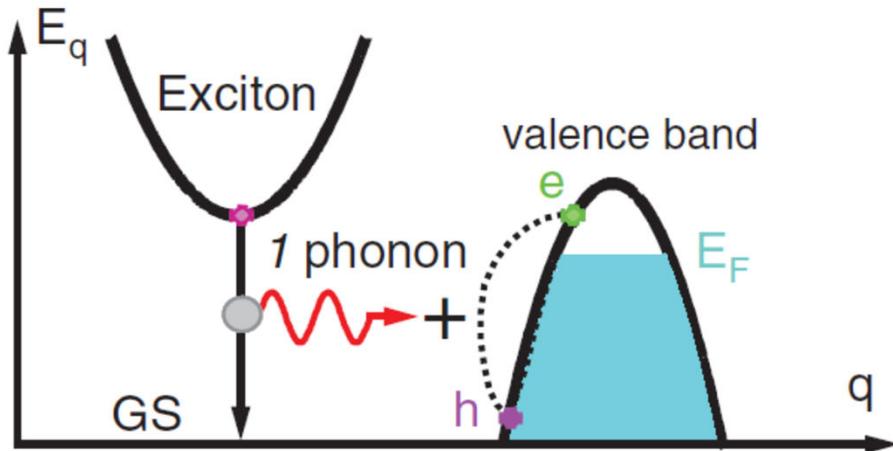
Exp: J. Christopher, et al.
Sci. Reports (2017)

Theory: Zhumagulov, et. al.
J. Chem. Phys. **153**,
044132 (2020)

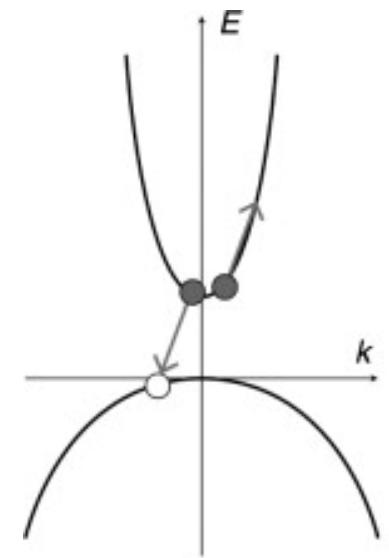
Outline

- 1) Linear spectroscopy due to excitons and trions
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Phonon-Assisted Exciton Ionization



Auger decay



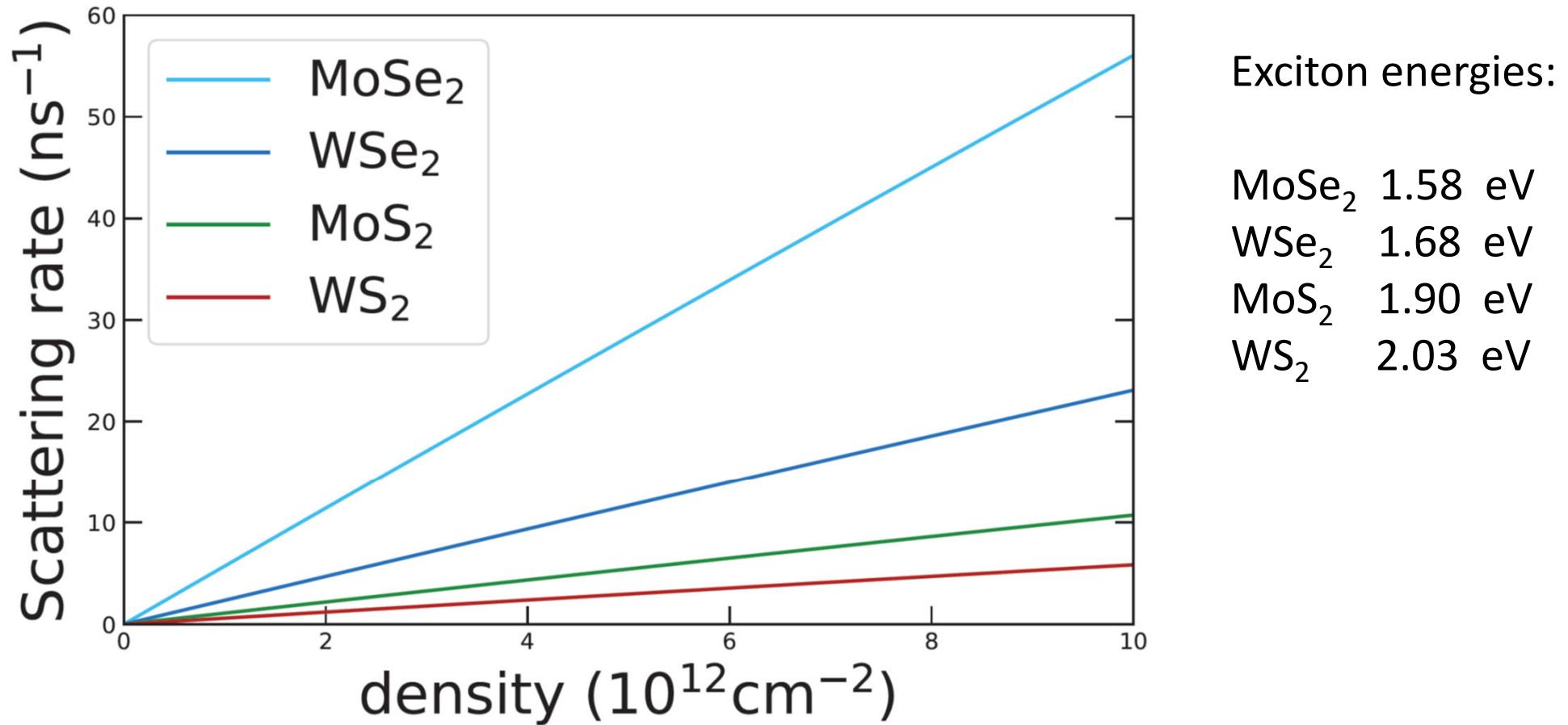
$$\frac{\hbar}{\tau} = \frac{2\pi g^2}{N^3} \sum_{c', \mathbf{k}', S, \mathbf{q}} f(\epsilon_{c_0} \mathbf{k}') [1 - f(\epsilon_{c'} \mathbf{k}' + \mathbf{q})]$$

$$\times \frac{\left| \sum_{cv\mathbf{k}} \mathcal{A}_{vc\mathbf{k}}^{S\mathbf{q}} U_{\mathbf{k}' + \mathbf{q}, \mathbf{k}', \mathbf{k} + \mathbf{q}, \mathbf{k}}^{c', c_0, c, v} \right|^2}{[\Omega_S(\mathbf{q}) - \Omega_S(\mathbf{0}) + \hbar\omega_{-\mathbf{q}}]^2}$$

$$\times \delta [\epsilon_{c' \mathbf{k}' + \mathbf{q}} - \epsilon_{c_0 \mathbf{k}'} + \hbar\omega_{-\mathbf{q}} - \Omega_S(\mathbf{0})]$$

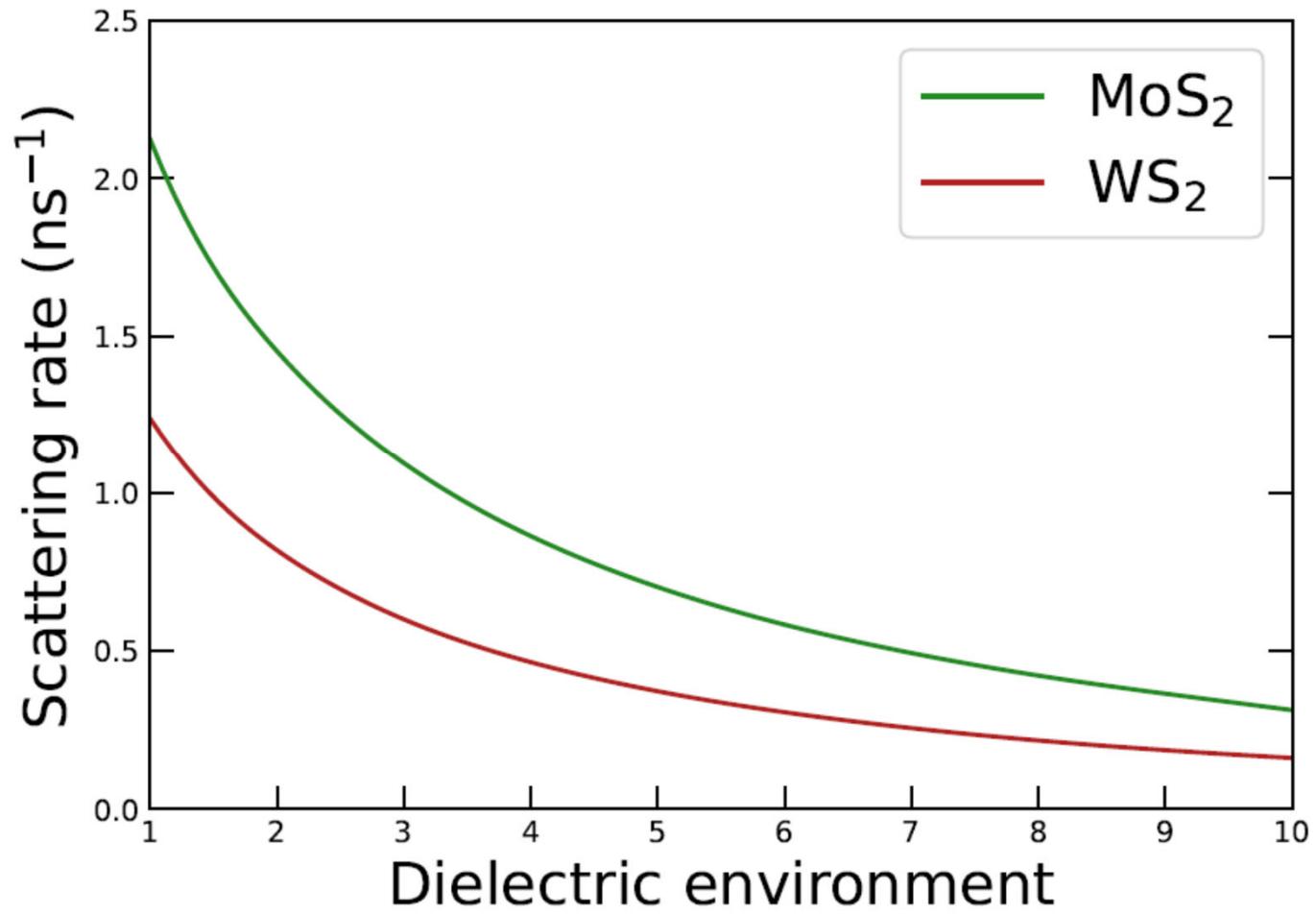
Perebeinos, Avouris, Phys. Rev. Lett. 101, 057401 (2008)

Phonon-Assisted Exciton Ionization in 2D materials



We use $\epsilon = 3.0$ corresponding to the experimentally observable exciton binding energy of ~ 300 meV

Phonon-Assisted Exciton Ionization in 2D materials



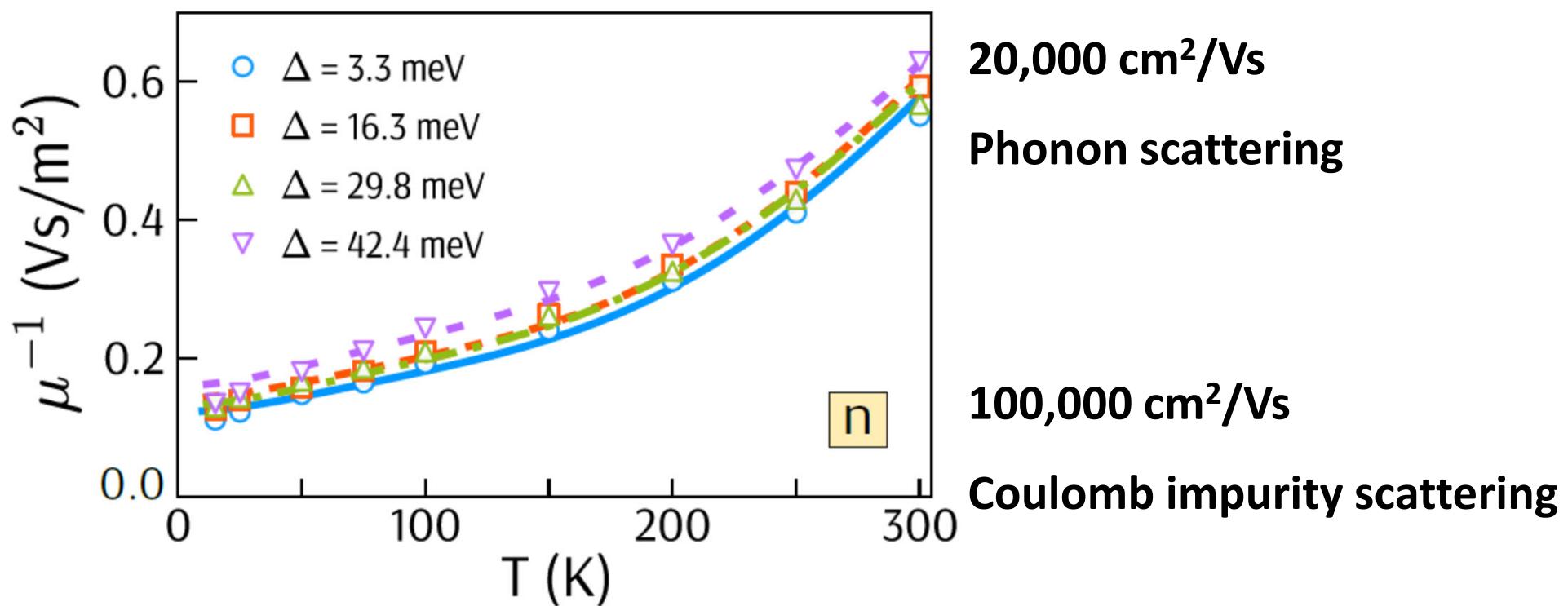
In the single-particle limit, i.e. $\epsilon = \infty$, phonon-assisted.
At fixed carrier density 10^{12} cm^{-2}

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motivation

High quality monolayer graphene have higher room temperature mobility than AB-stacked bilayer graphene and exhibit stronger temperature dependence.



which phonon is responsible for in-plane transport?

$$eF \frac{\partial f_k}{\partial \hbar k} = - \sum_{k'} S_{kk'} f_k (1 - f_{k'}) - S_{k'k} f_{k'} (1 - f_k)$$

Boltzmann transport equation

Electron-phonon scattering

$$S_{kk'}^\mu = \left| \left\langle \psi_k \left| H_{e-ph}^\mu \right| \psi_{k'} \right\rangle \right|^2 [n_{k-k',\mu} \delta(E_{k'} - E_k + \hbar\omega_{k-k',\mu}) + (1 + n_{k'-k,\mu}) \delta(E_{k'} - E_k - \hbar\omega_{k'-k,\mu})]$$

$$t_{ij} = t_0 - g \delta r_{ij}, \quad t_0 = 3.1 \text{ eV}, \quad g = 5.3 \text{ eV/Ang}$$

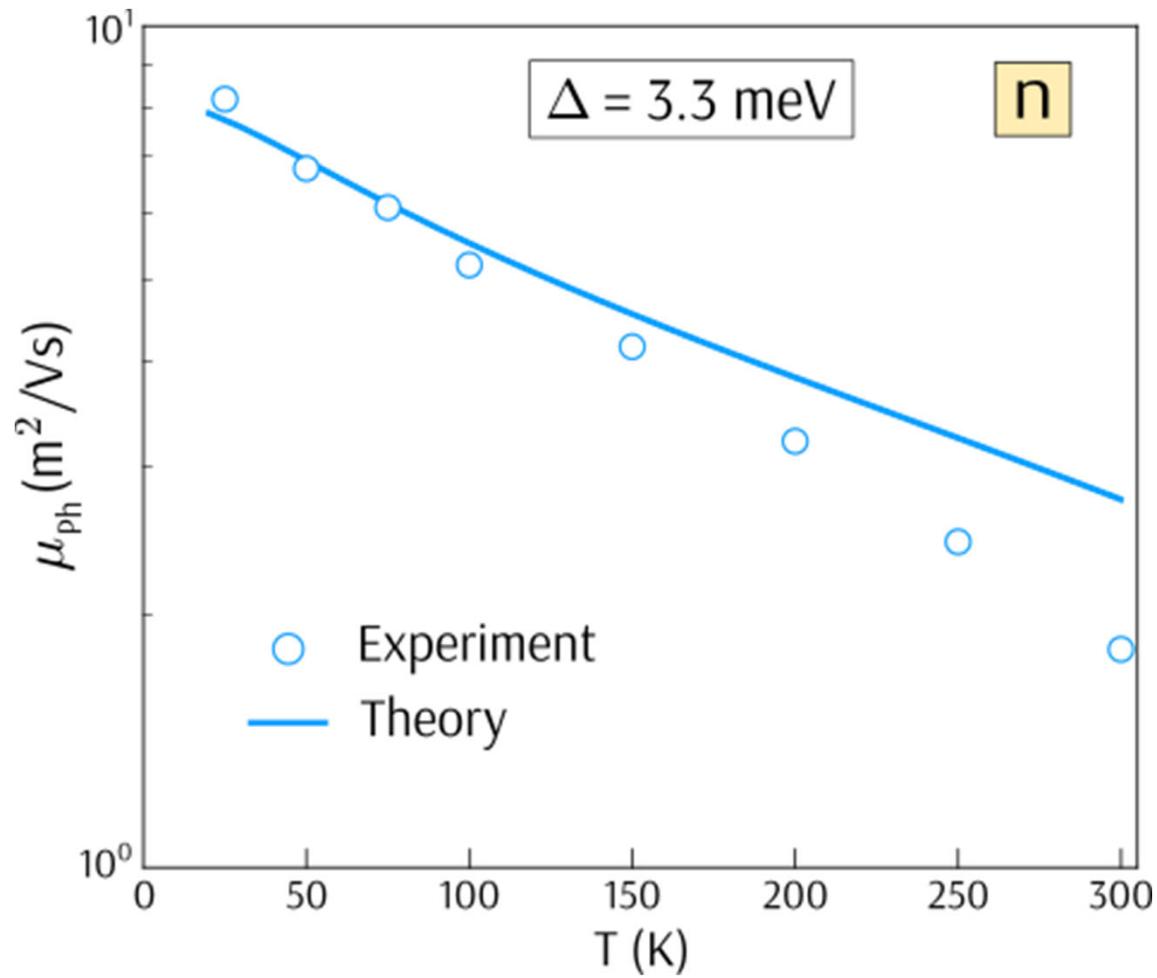
$$t_{ij} = t_\perp \exp \left\{ \left(- \frac{r_{ij} - h_0}{\lambda_z} \right) \right\} \exp \left\{ \left(- \left(\frac{\xi_{ij}}{\lambda_{xy}} \right)^\alpha \right) \right\}$$

Model parameters

Electron-phonon coupling: Perebeinos et. al. PRL 109, 236604 (2012)

Phonons: Perebeinos and Tersoff, PRB 79, 241409(R) (2009)

Intrinsic only phonon limited transport



Perfect match at low temperatures

Deviations at $T > 150 \text{ K}$

Surface Polar Phonon scattering in h-BN

Robust solution: Maxwell's equation
for electric field

$$\varphi(\vec{\xi}, z) = \sum_{\vec{q}} \varphi(z) e^{i \vec{q} \cdot \vec{\xi}} \quad \omega_{SPP} = \omega_{TO} \sqrt{\frac{\varepsilon_0 + \gamma(q)}{\varepsilon_\infty + \gamma(q)}}$$

$$\varphi(z) = \begin{cases} \varphi_0 \cosh(q_z z) & |z| < h_s \\ Ae^{q(z-d)} + Be^{-q(z-h_s)} & h_s \leq z < d \\ Ce^{-q(z-d)} & d \leq z \end{cases}$$

$$\frac{1}{L^2} \frac{\hbar}{2\omega} = \int \frac{1}{4\pi} \frac{1}{2\omega} \left(\frac{\partial \epsilon}{\partial \omega} |\mathbf{E}_\perp|^2 + \frac{\partial \epsilon}{\partial \omega} |\mathbf{E}_\parallel|^2 \right) dr$$

$$|M_{\mathbf{k}\mathbf{q}}|^2 = (e\varphi_0)^2 |\langle \psi_{\mathbf{k}} | \psi_{\mathbf{k}+\mathbf{q}} \rangle|^2$$

$$(e\varphi_0)^2 = \frac{\pi e^2}{q A_C N_k} \hbar \omega \left(\frac{1}{\varepsilon_\infty + \gamma(q)} - \frac{1}{\varepsilon_0 + \gamma(q)} \right) f^2$$

$$f^{-1} = \cosh(q_z h_s) \cosh(q(d - h_s)) \gamma_2(q),$$

See also:

Hess

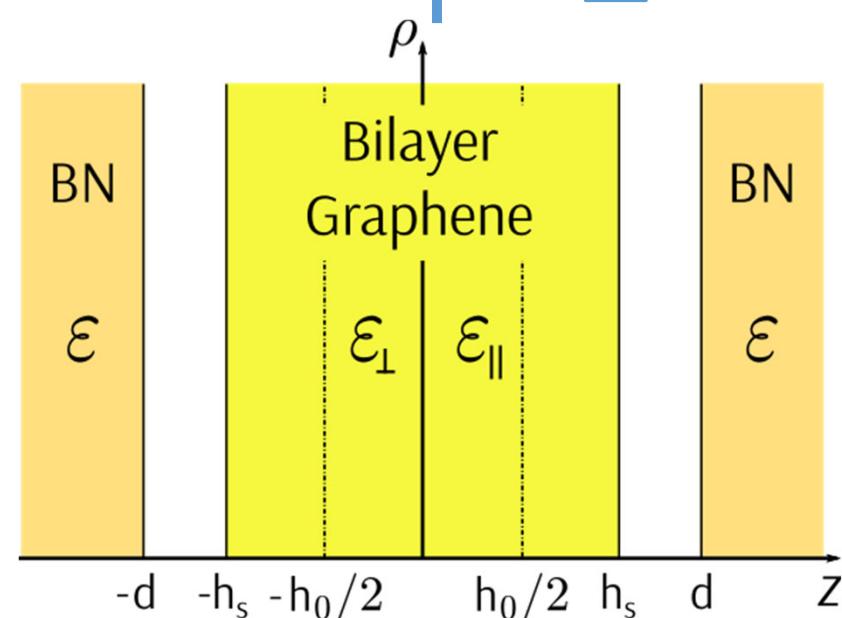
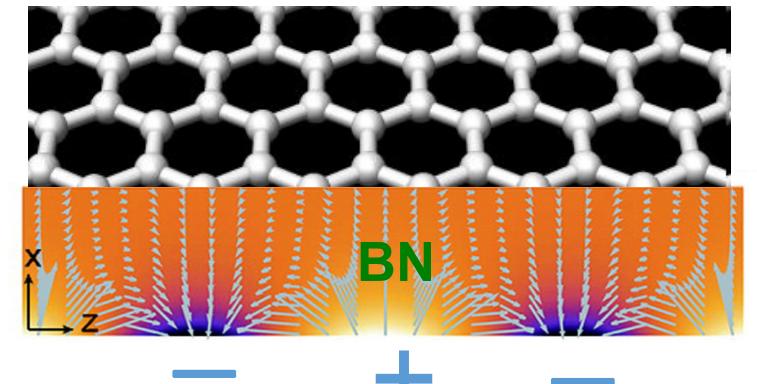
Fischetti

Konar, Frantini

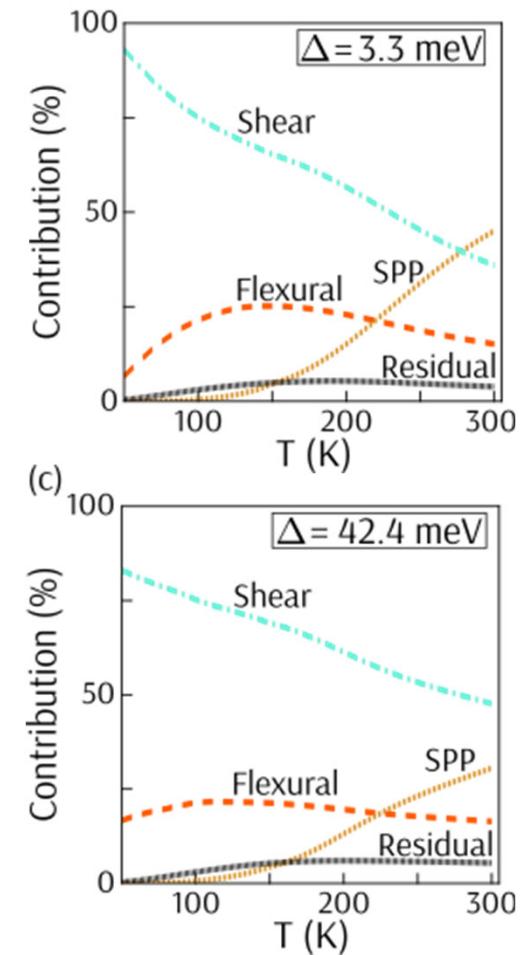
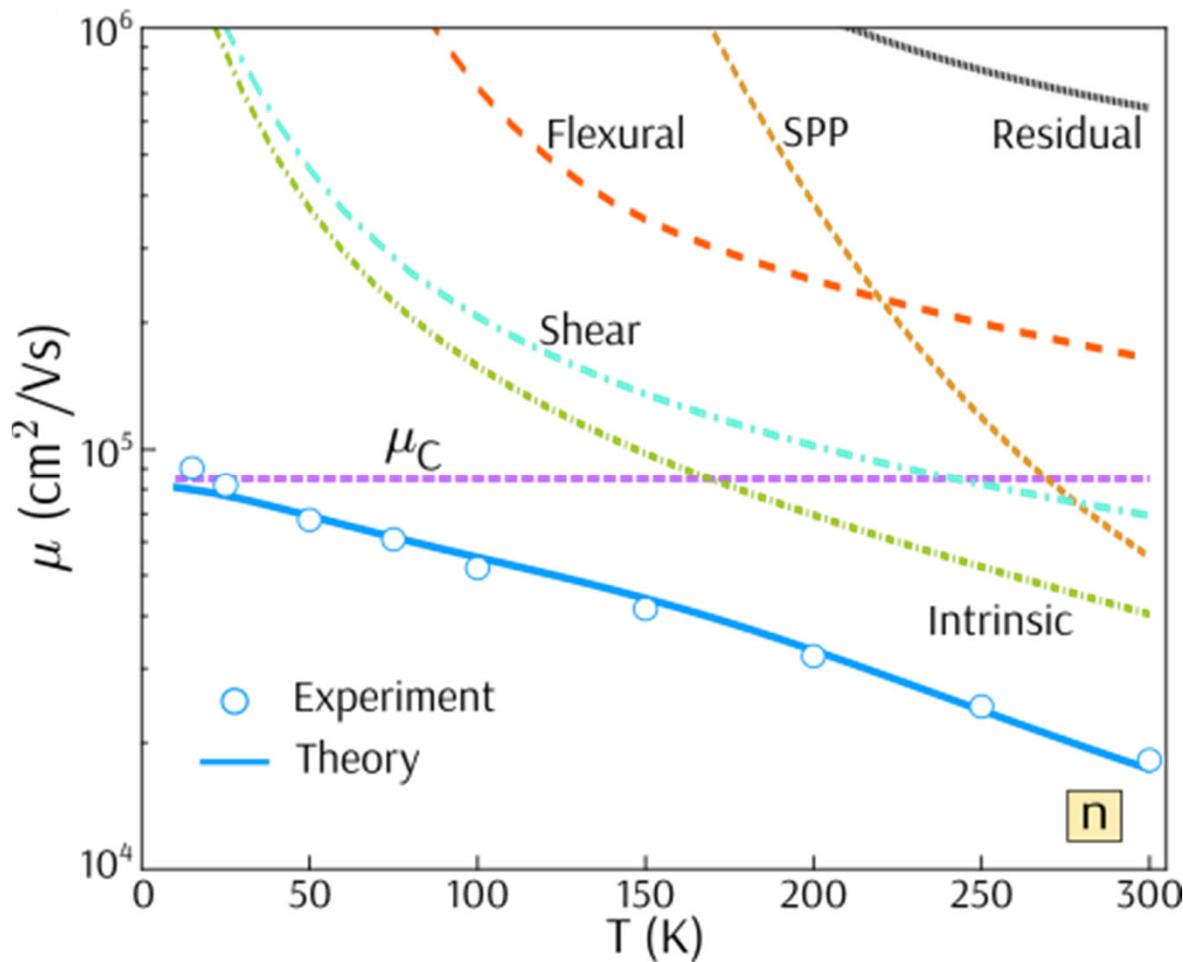
V. Perebeinos et. al. Phys. Rev. B **81**, 195442 (2010)

Intuitive arguments

$$P(\vec{r}') \propto \frac{1}{\varepsilon_\infty + 1} - \frac{1}{\varepsilon_0 + 1} \quad V_{SPP}(q) \propto \frac{e^{-qz_0}}{\sqrt{q}} P$$



phonon-limited mobility in bilayer graphene relative contributions of different modes



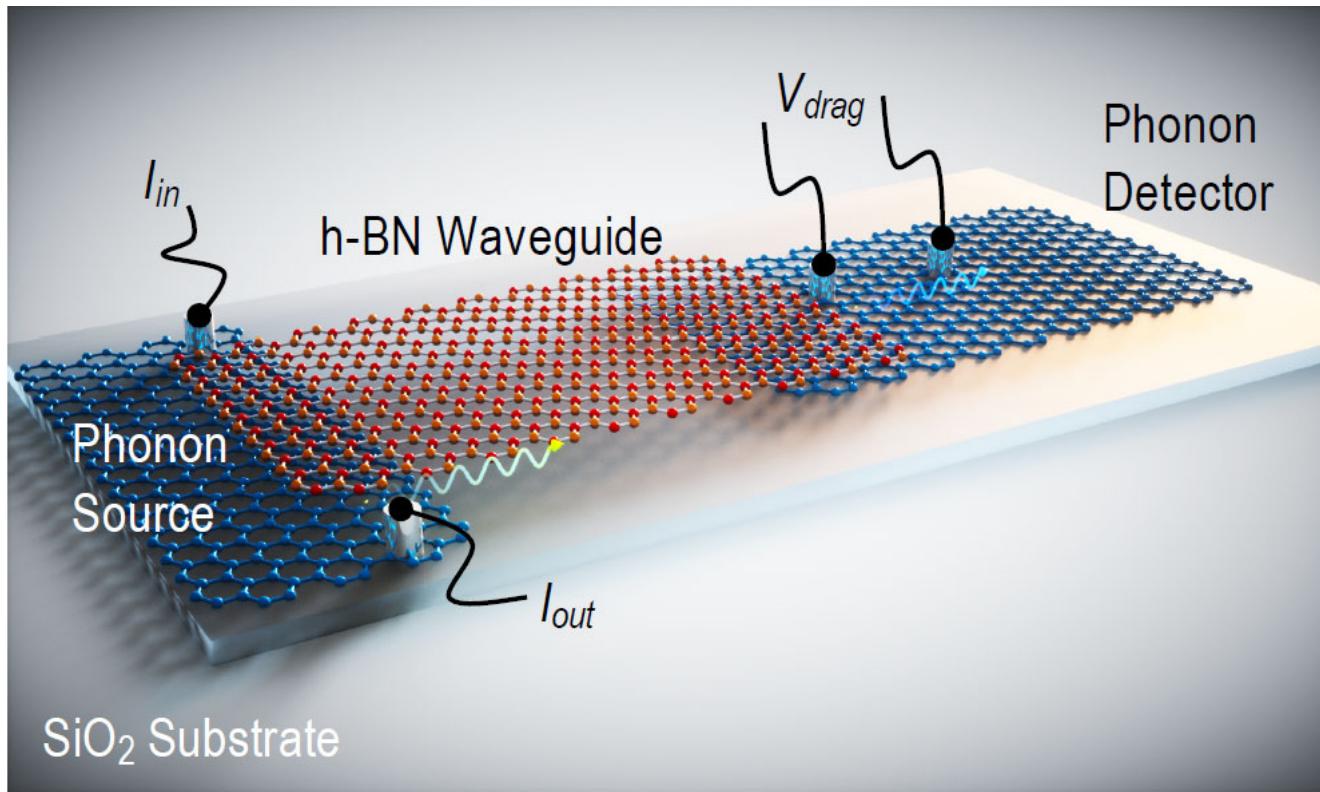
remote phonon sensing

make one phonon out of equilibrium: $n(q_0) = n_{eq}(q_0) + 1$

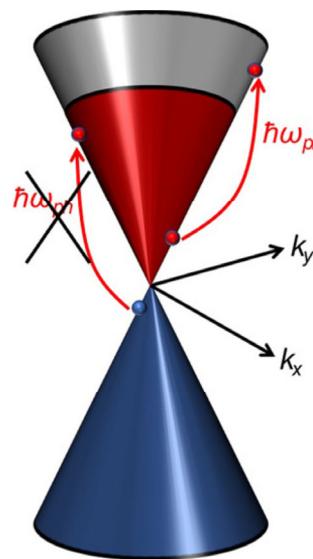
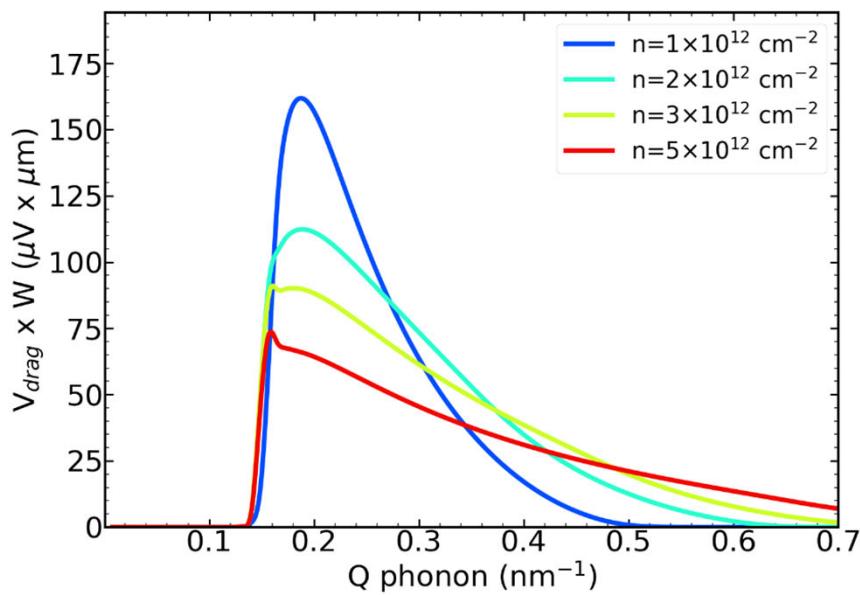
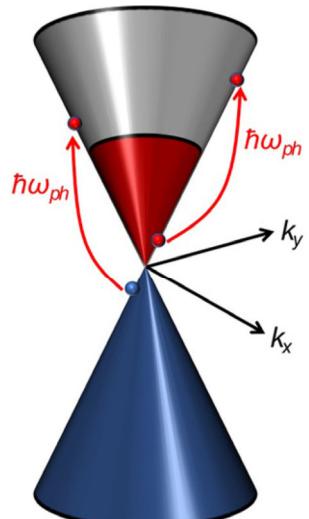
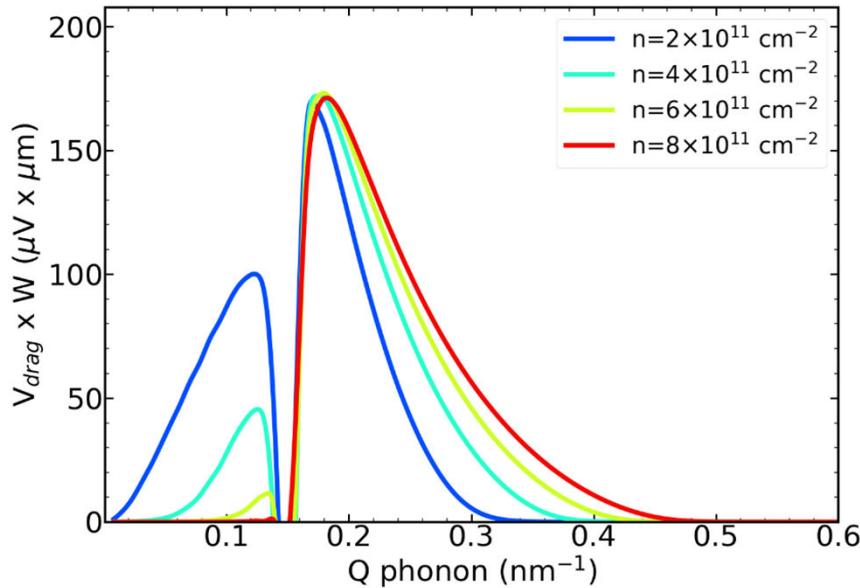
$$\vec{v}_\alpha(k) \frac{\partial f_\alpha(k, r)}{\partial \vec{r}} + e \vec{F} \frac{\partial f_\alpha(k, r)}{\partial \hbar \vec{k}} = \left(\frac{\partial f_\alpha(k)}{\partial t} \right)_{e-ph} + \left(\frac{\partial f_\alpha(k)}{\partial t} \right)_{imp}$$

$$\vec{v}_\lambda(q) \frac{\partial n_\lambda(q, r)}{\partial \vec{r}} = \left(\frac{\partial n_\alpha(q)}{\partial t} \right)_{e-ph} + \left(\frac{\partial n_\alpha(q)}{\partial t} \right)_{ph-ph \& ph-imp}$$

$$V_{drag} = \frac{e \sum_\alpha \int f_\alpha(k) v_\alpha(k) d\vec{k}}{\sigma W}$$



drag voltage in monolayer graphene on semi-infinite BN

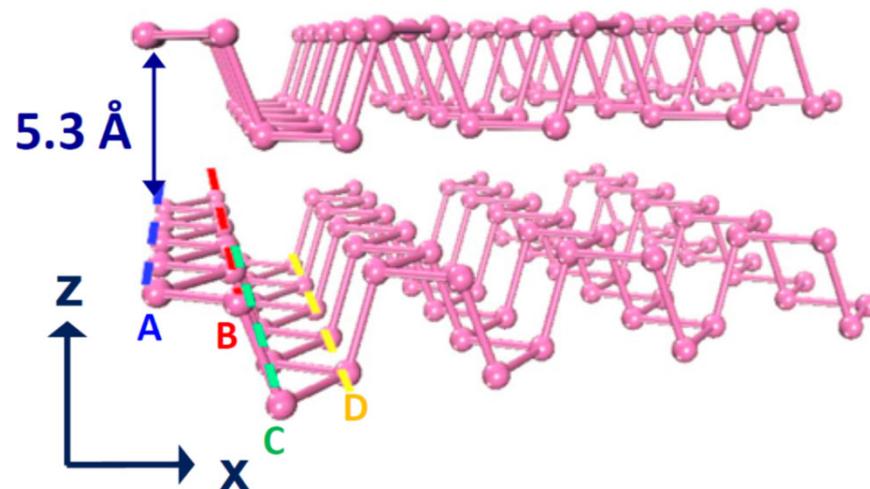


Kefayati, Bird, Perebeinos
PRB **106**, 155415 (2022)

Outline

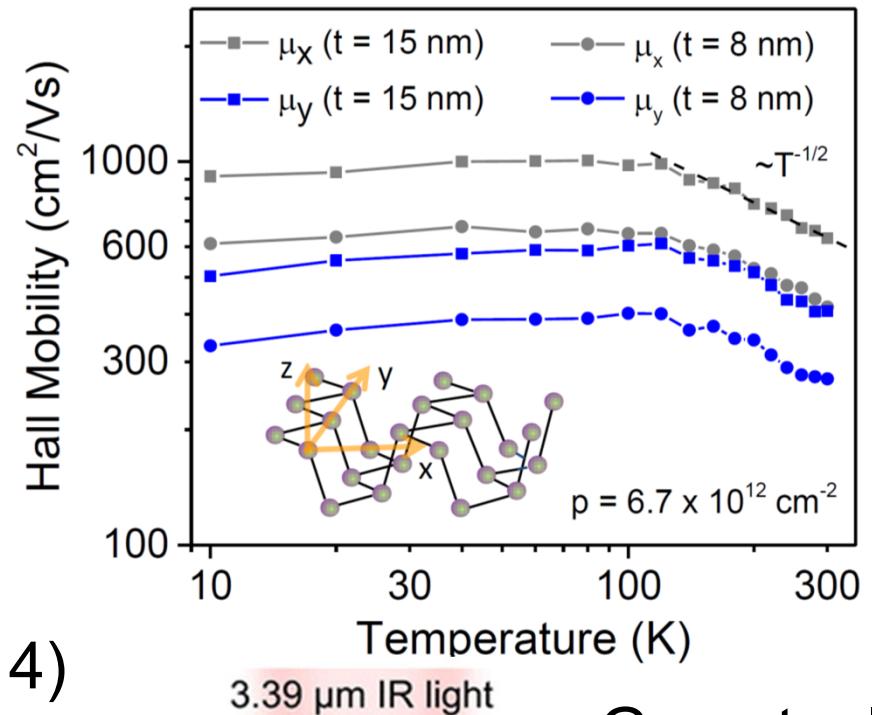
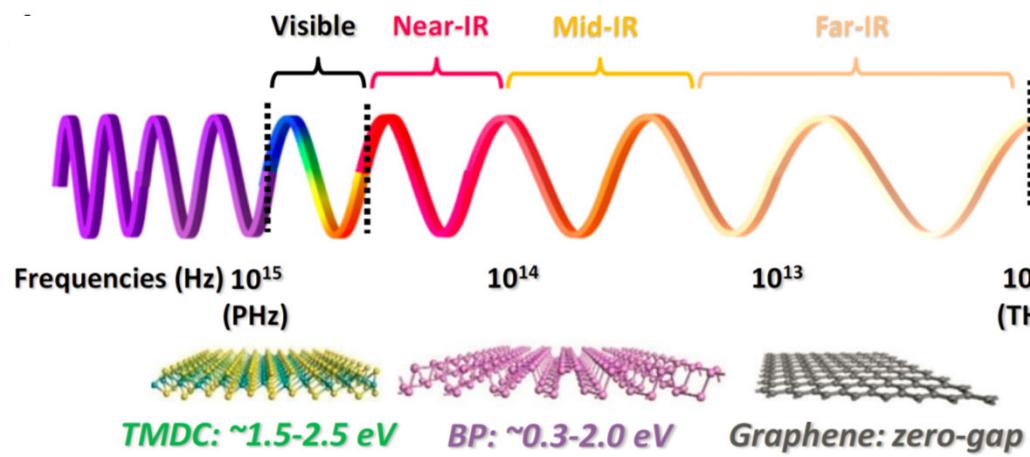
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- 4) Electron-phonon interactions in black phosphorous and 1D SbPS4

quest for other 2D materials: black phosphorous

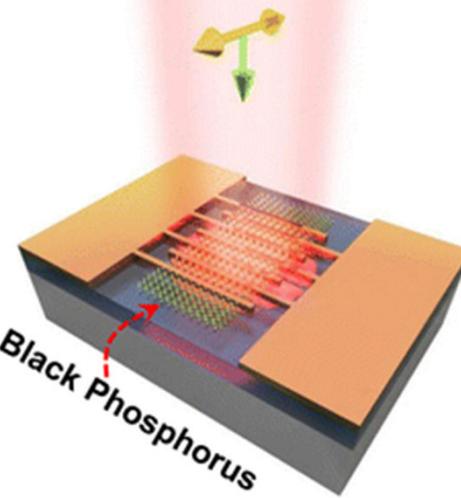


Ling et. al. PNAS (2015)

Xia et. al. Nature Com. (2014)

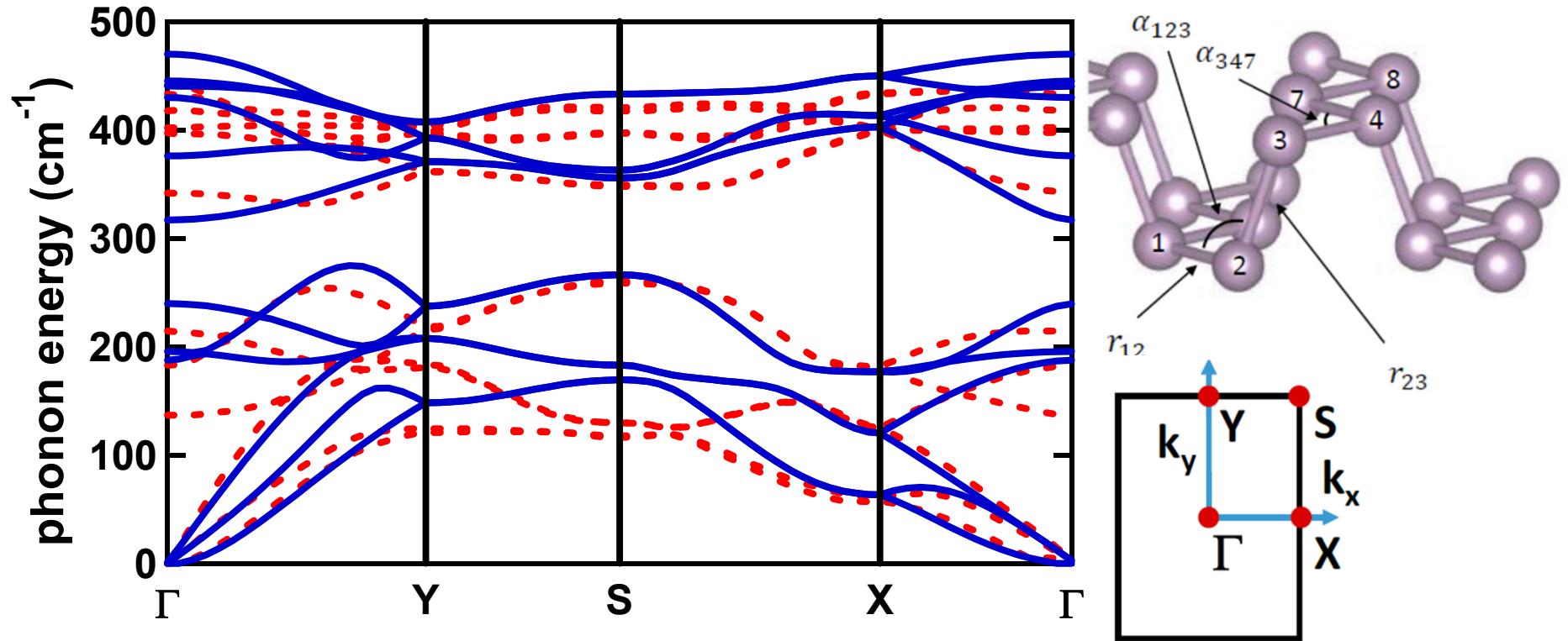


3.39 μm IR light



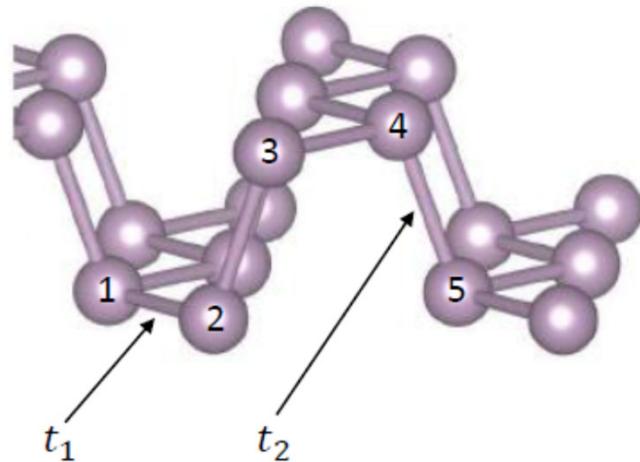
Guo et. al.
Nano Lett.
(2016)

Black Phosphorous: phonons



$$H_{ph} = \frac{k_1}{2} (\delta r_{12}^2 + \delta r_{23}^2 + \dots) + \frac{k_2}{2} (\delta \alpha_{123}^2 + \delta \alpha_{347}^2 + \dots)$$

Black Phosphorous: band structure

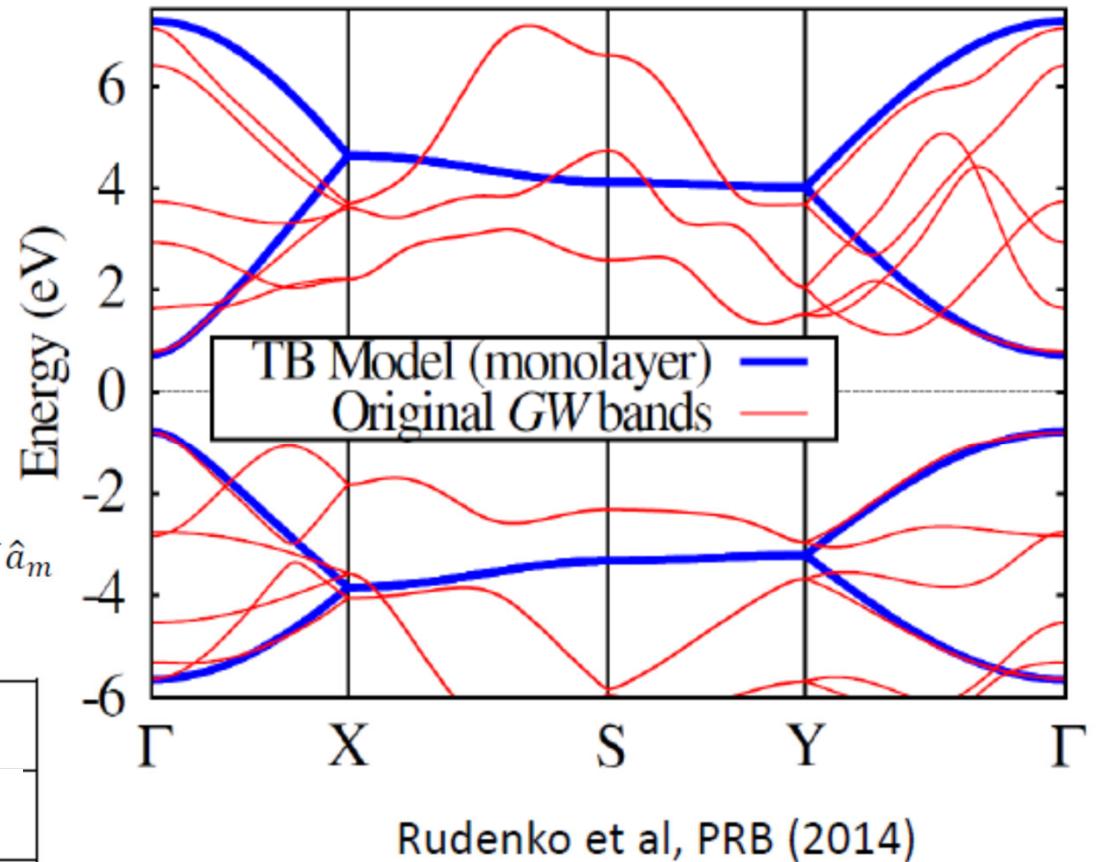


Tight binding:

$$\hat{H} = \sum_{i,k,l,m} t_1 \hat{a}_i^\dagger \hat{a}_k + t_2 \hat{a}_l^\dagger \hat{a}_m$$

Best fit:

t1, eV	t2, eV
-1.15	3.07



	E_g (eV)	m_{xh}	m_{yh}	m_{xe}	m_{ye}
GW Rudenko (2014)	1.60	-0.18	-1.14	0.17	0.85
our model	1.54	-0.15	-1.17	0.15	1.17

electron - phonon interaction

$$\hat{H}_{el-ph} = \sum_{k_i k_f, q} g_1 M_1 \hat{a}_{k_f}^+ \hat{a}_{k_i} (\hat{c}_q + \hat{c}_{-q}^+) \hat{c}_q + g_2 M_2 \hat{a}_{k_f}^+ \hat{a}_{k_i} (\hat{c}_q + \hat{c}_{-q}^+) + c.c.$$

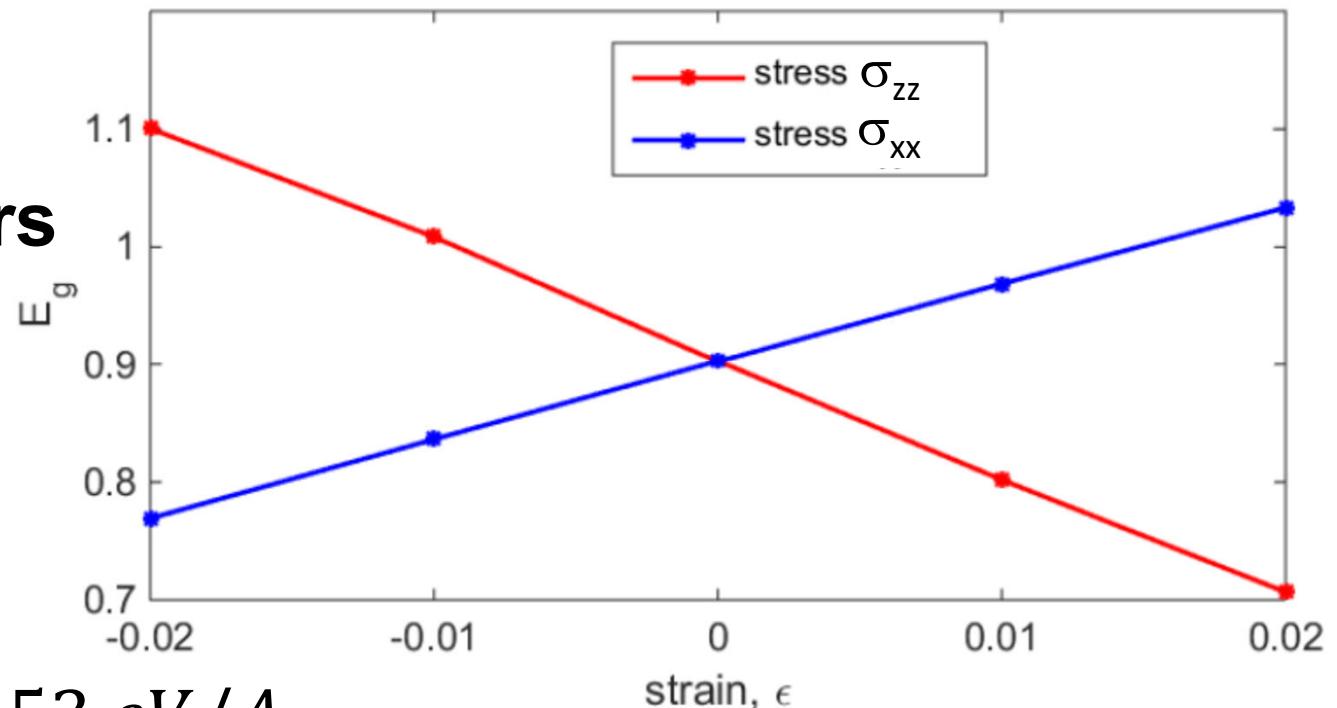
our DFT results

e-ph parameters

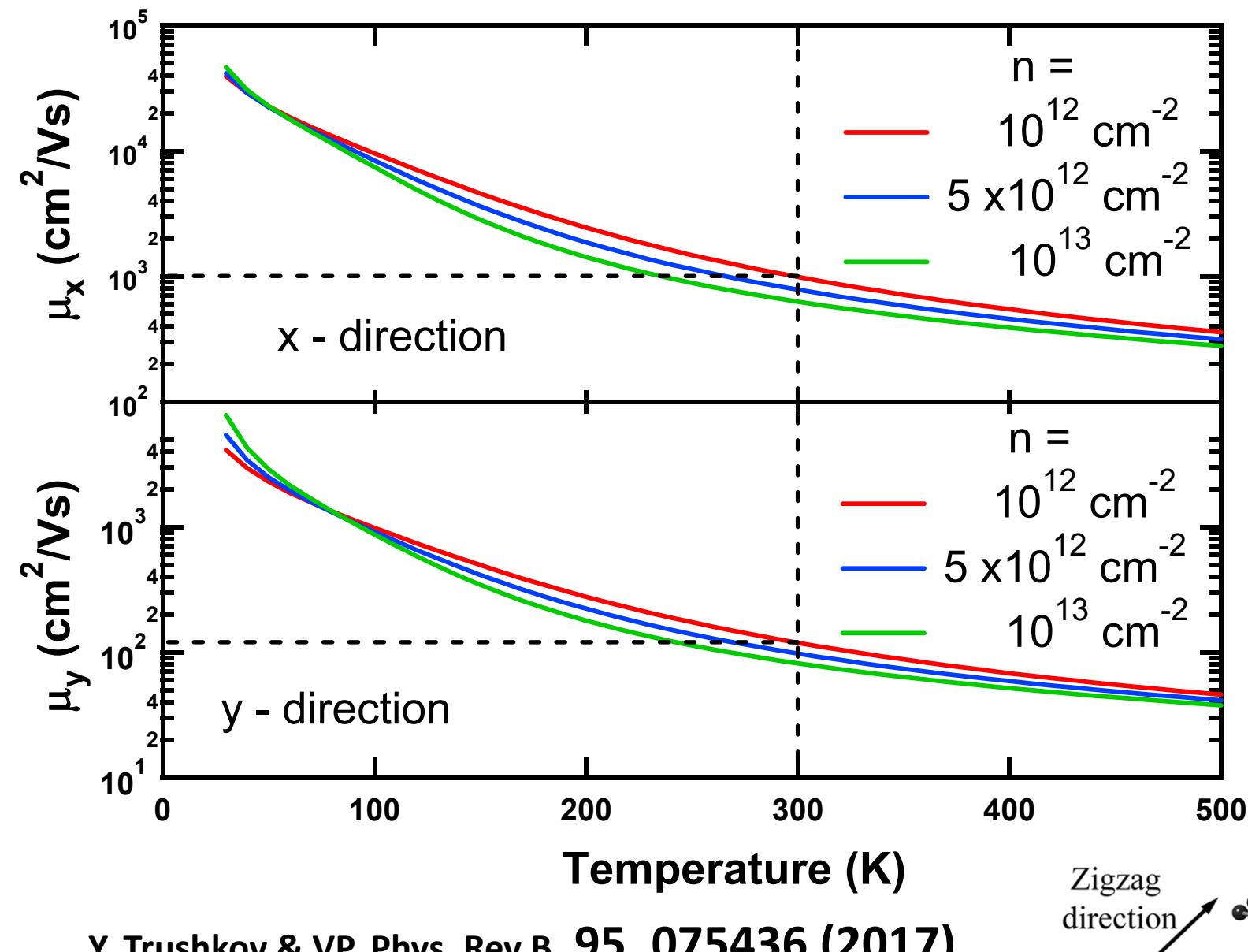
$$E_g = 2t_2 - 4|t_1|$$

$$g_1 = -\frac{\partial |t_1|}{\partial r_1} = 1.53 \text{ eV/A}$$

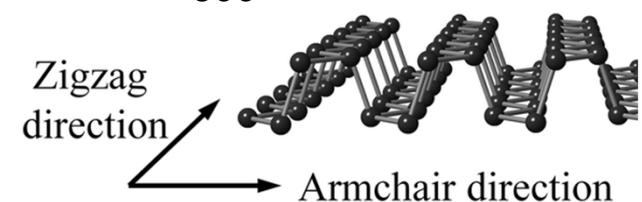
$$g_2 = -\frac{\partial |t_2|}{\partial r_2} = 2.46 \text{ eV/A}$$



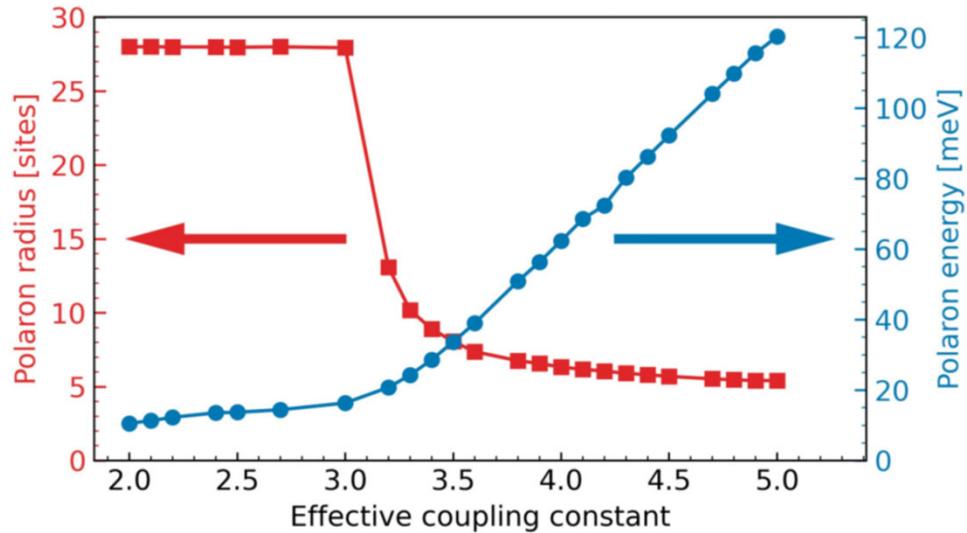
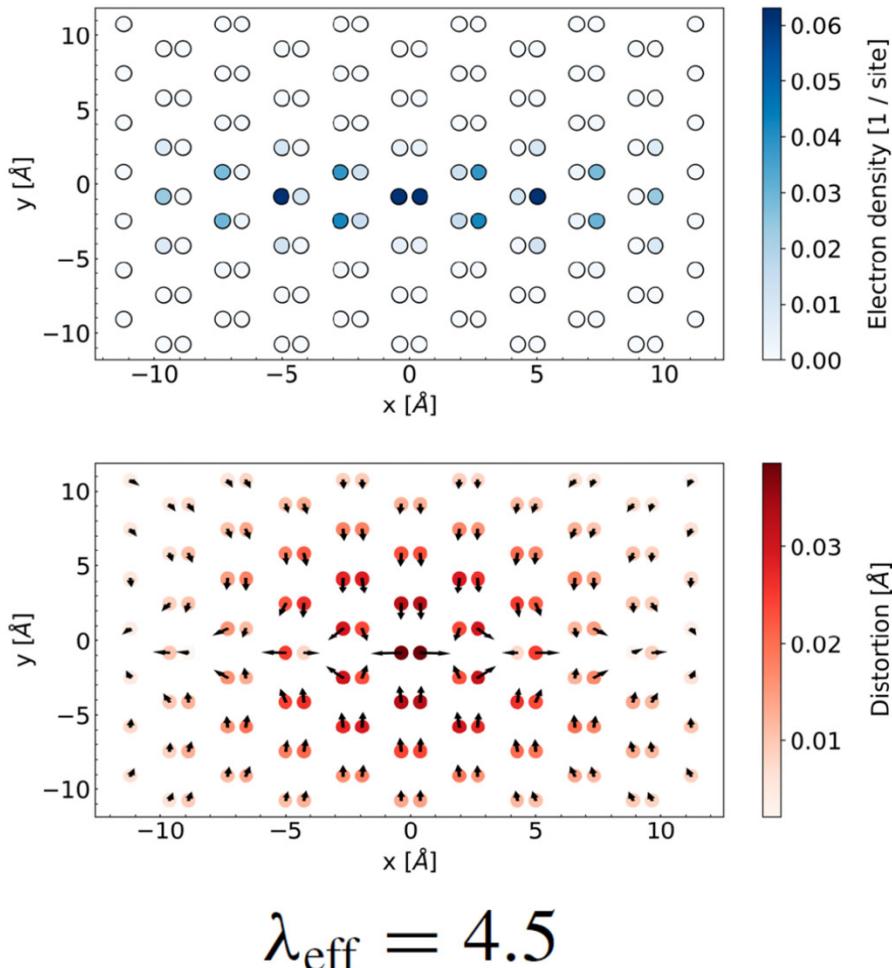
phonon limited low field mobility



Y. Trushkov & VP, Phys. Rev B. 95, 075436 (2017)



Polarons in BP



$$\lambda_{\text{eff}} = \frac{1}{2k_1} \left(\frac{g_1^2}{|t_1|} + \frac{g_2^2}{|t_2|} \right) \approx 0.278$$

Neverov et. al. Phys. Rev Materials 5, 054008 (2021)

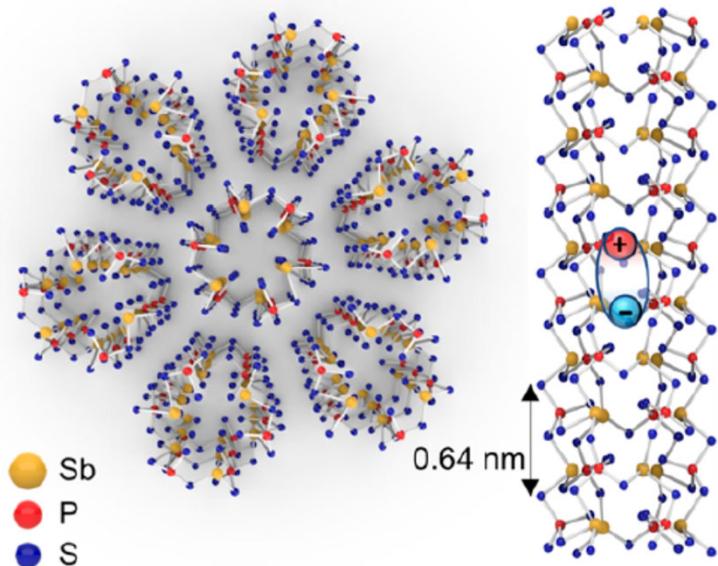
See also: Vasilchenko et. al.

J. Phys. Chem. Lett. 12, 4674 (2021)

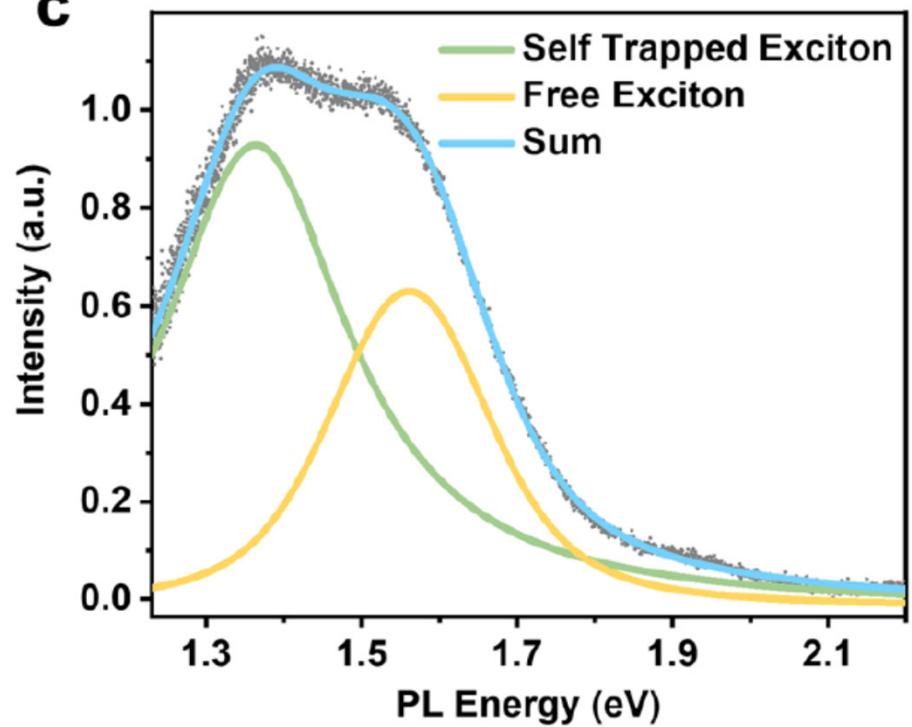
Using parameters in Y. Trushkov & VP, Phys. Rev B. 95, 075436 (2017)

Polarons in 1D SbPS₄

a



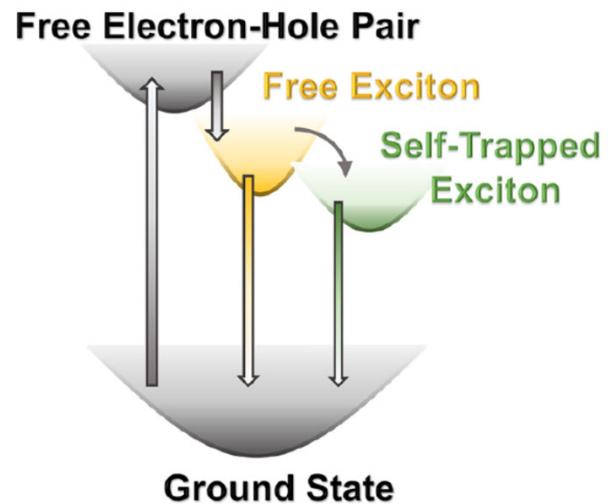
c



$$E_P = \sum_v \frac{C_v^2}{k_v}$$

polaron binding ~ 150 meV

$$E_b = A_b R^{\alpha-2} m^{\alpha-1} \epsilon^{-\alpha} \quad \text{exciton binding } \sim 1 \text{ eV}$$



acknowledgment

Optical response and polaritons in 2D materials:

Yaroslav Zhumagulov², Dmitry Gulevich³, Alexei Vagov³



Polarons and e-ph interactions in BP:

Yuri Trushkov⁴, Viacheslav Neverov⁵, Alexander Lukyanov⁵, Andrey Krasavin⁵

Polarons in SbPS4:

Davoud Adinehloo¹, Tai Kong⁶, John Schaibley⁶, et. al.



Phonon-assisted Auger decay of excitons: *Benedict Scharf⁷*

Electron-phonon interactions in 2D materials: *Cheng Tan⁸, Davoud Adinehloo¹, James Hone⁸, Ali Keifayati¹, Jon Bird¹*

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⁵MEPhI, ⁶University of Arizona, ⁷Universität Würzburg, ⁸Columbia University

Summary

- 2D materials offer tunable and versatile solid-state material platform for quantum photonics and quantum phononics
- 2D materials optical response is dominated by excitons and trions described by two and three-particle Bethe-Salpeter and Tamm-Dancoff equations with predictive power
- Phonon-Assisted Indirect Exciton Ionization is predicted to have a sub ns lifetime at realistic doping levels
- Low dimensionality leads to enhanced polaronic effects in materials like SbPS4